

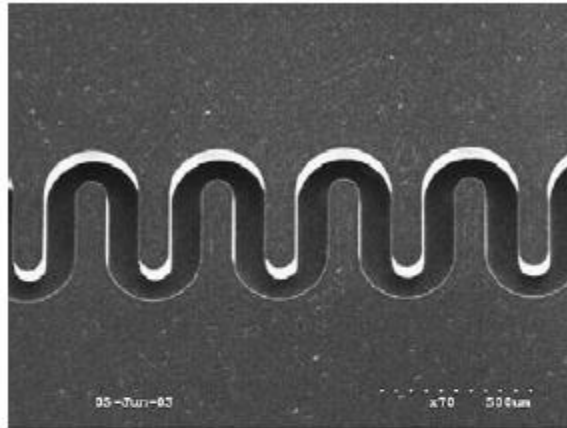
Microfabrication for fluidics

sami.franssila@aalto.fi

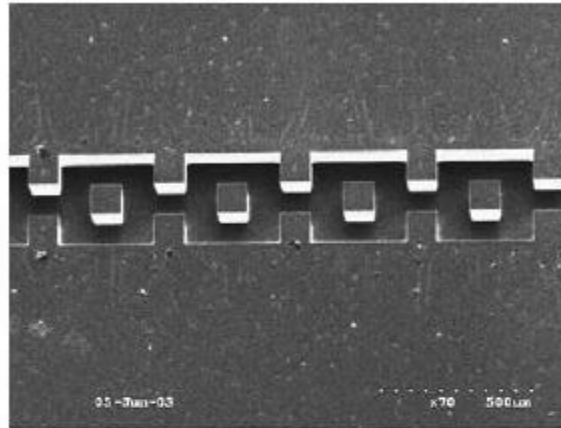
Contents

- Optical lithography
- Etching
- Polymer replication
- Bonding
- Thin films
- Structure-materials-processes pros & cons
- Materials property comparison

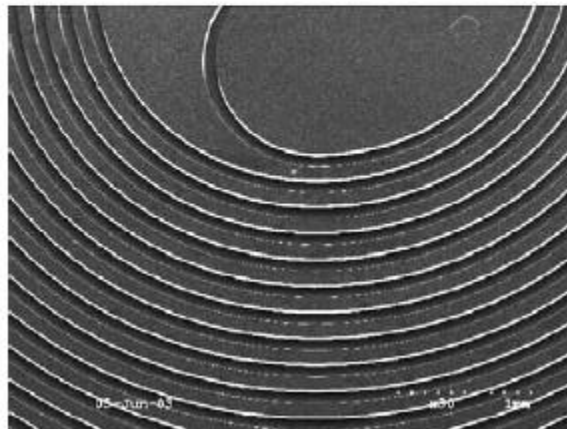
Channels, top view (layout view)



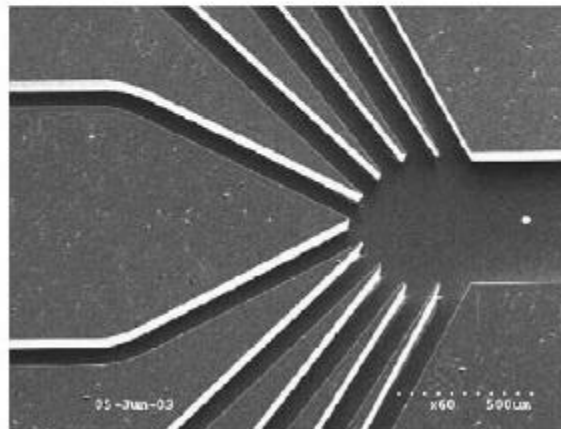
(a)



(b)



(c)



(d)

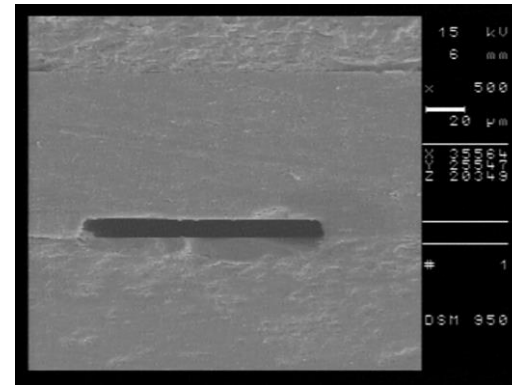
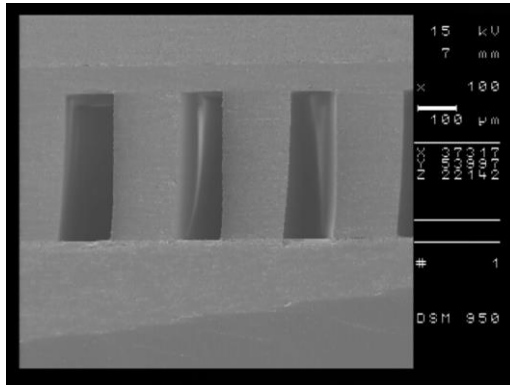
Typical scales:

Individual channels
10-100 μm wide

Large reservoirs:
millimeter sizes
(volume 0.1 nl if
100 μm high)

Channels, cross section view

SU-8
epoxy
polymer



Typical
channel
heights:

5-500 µm

Glass

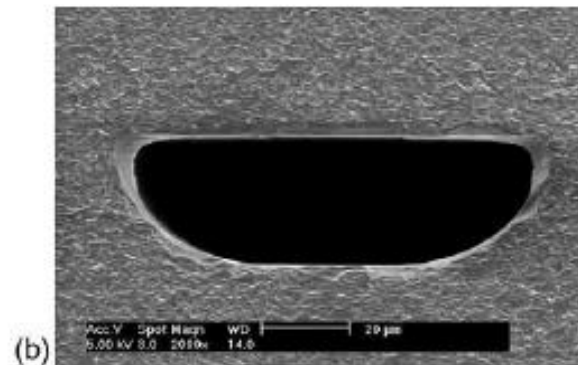
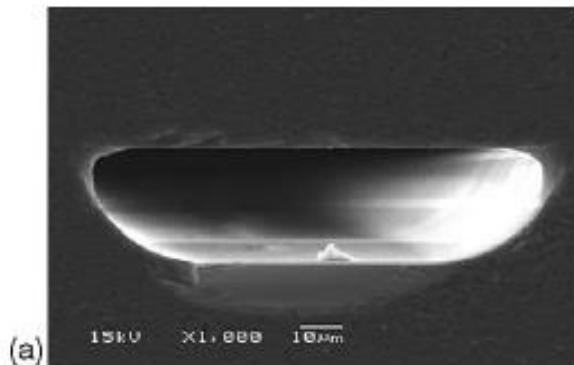
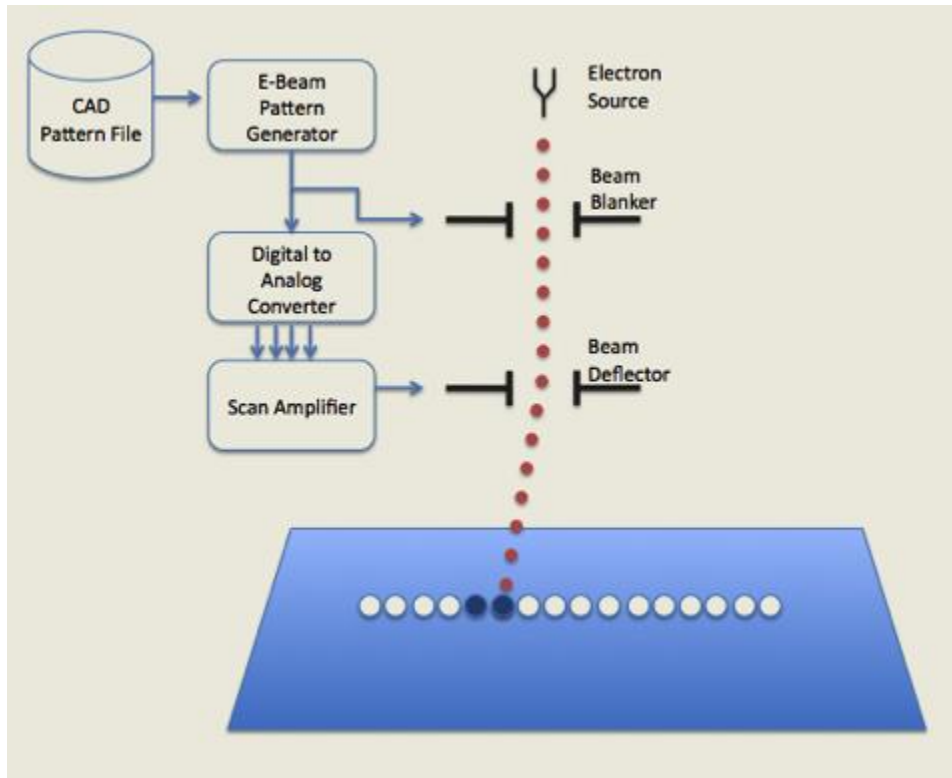


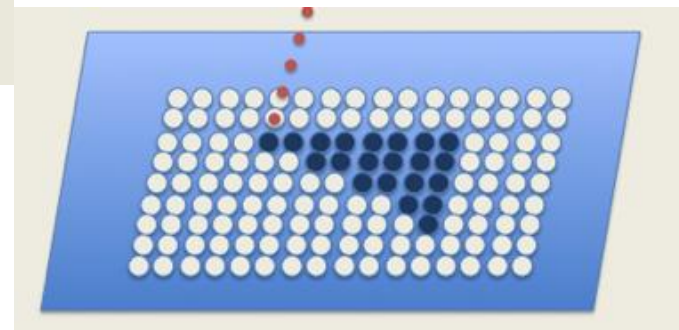
Fig. 6. SEM images of the cross-section of a microchannel in (a) quartz and (b) glass.

Original pattern generation



Laser/electron beam exposes polymer pixel-by-pixel, creating desired shapes.

Pixel-by-pixel the pattern emerges, slowly. Writing time hours, even days.



Creating a photomask



Laser/e-beam has caused local polymerization, which leads to solubility difference.

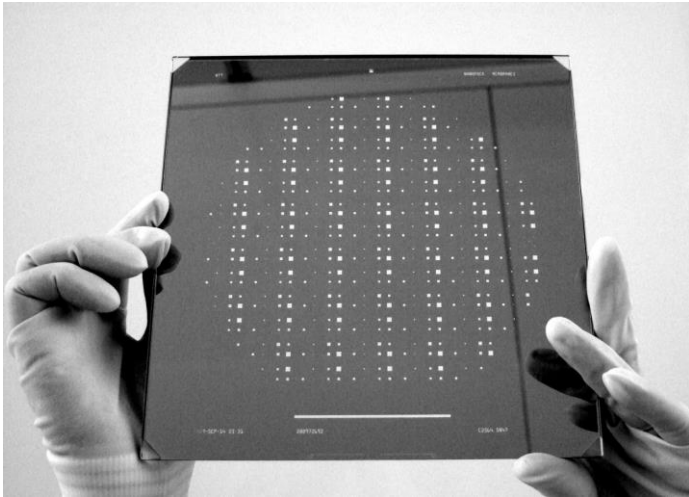


Polymer acts as a protective coating during Cr acid etching.

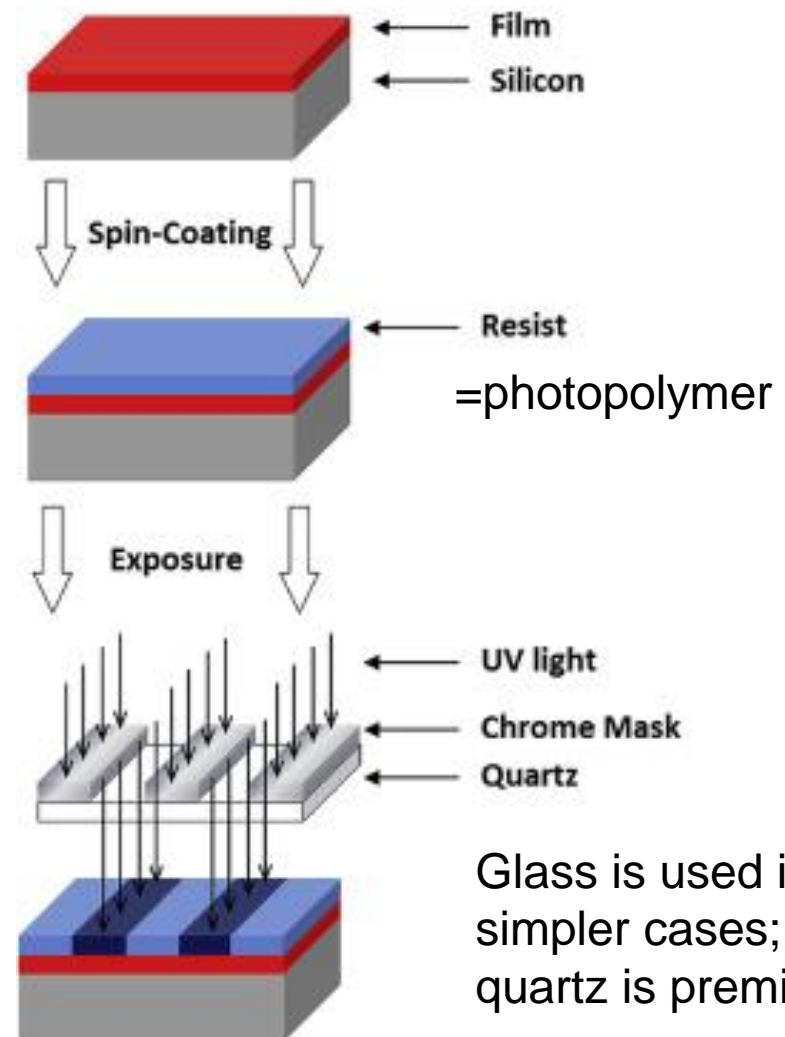


Polymer is removed, and we have Cr-pattern on glass plate. We call this a photomask.

Patterning with a mask



Photomask = glass plate with metal patterns (=opaque areas) and open areas (=transparent at UV-VIS wavelengths)

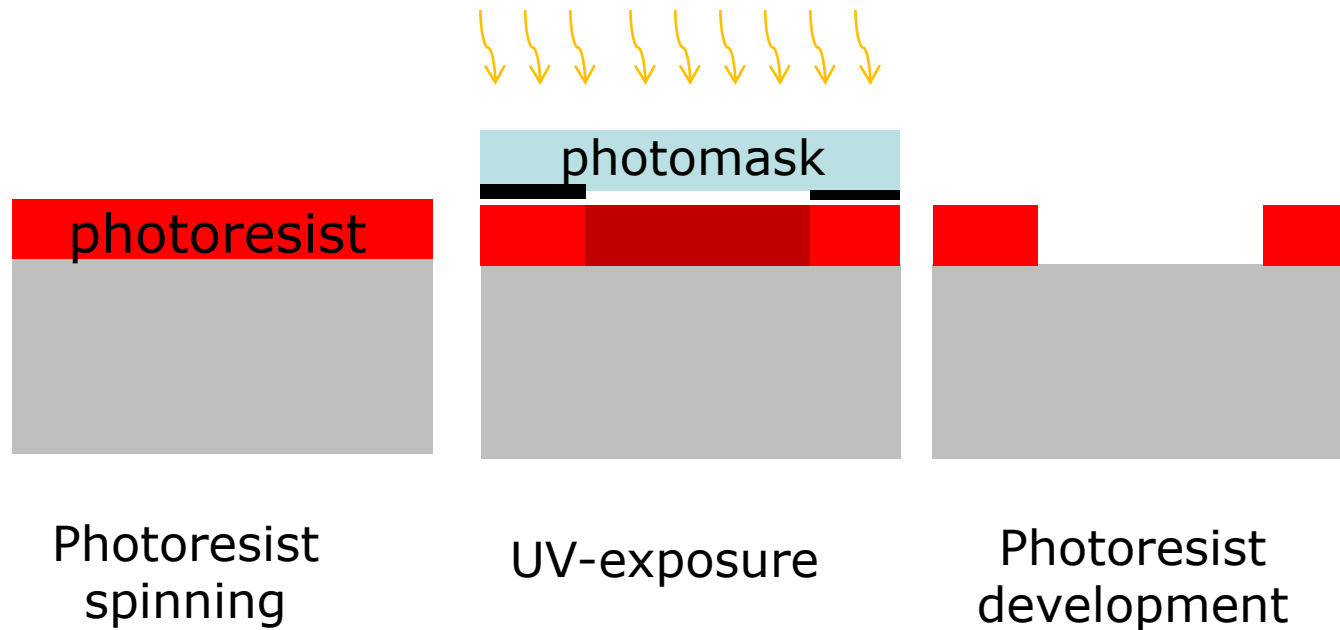


Lithographic patterns

Spin coat photoresist (photoactive polymer)

Expose thru mask with UV light (solubility changes)

Develop: exposed parts solubility differs from non-exposed → pattern emerges



Mask cost vs. feature size

Office laser printer enables ~ 100 μm wide lines	0.1 €
Industrial laser printer ~ 10 μm wide lines	10 €
Dedicated microfabrication laser ~ 1 μm wide lines	1000 €
Electron beam system ~ 0.1 μm wide lines	10 000 €

Most microfluidic structures are in
10-100 μm range

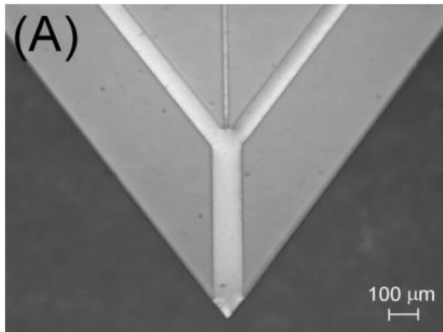
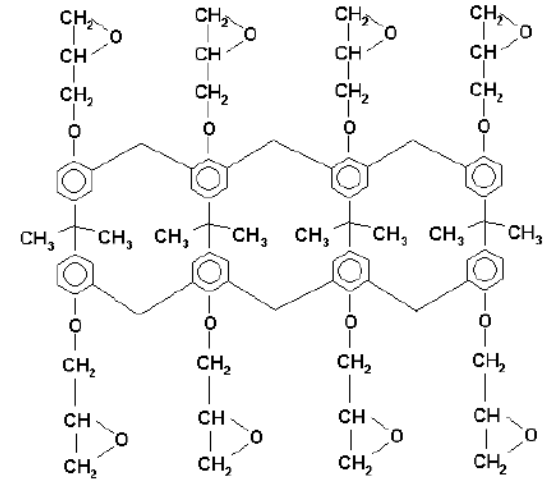
Fabrication example 1:

SU-8 Fabrication by UV-lithography

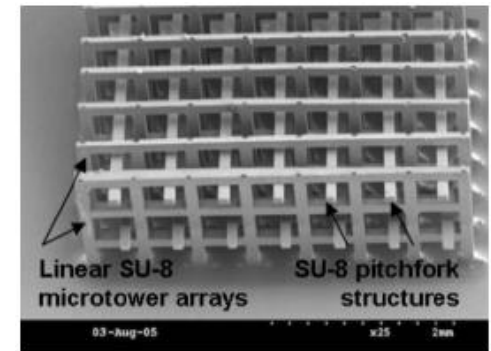
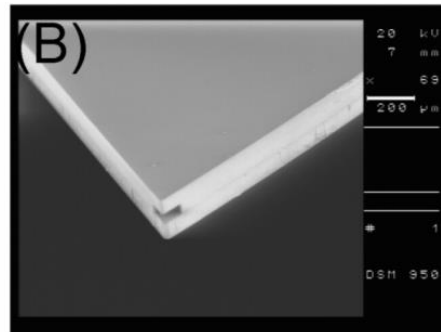
The SU-8 resist contains 3 principal components:

- Resin (defines mechanical & thermal properties)
- Photoinitiator (defines optical properties)
- Solvent (defines viscosity)

- Wide range of possible thicknesses by spin coating 100 nm – 1 mm



SU-8 electro spray ionization tip



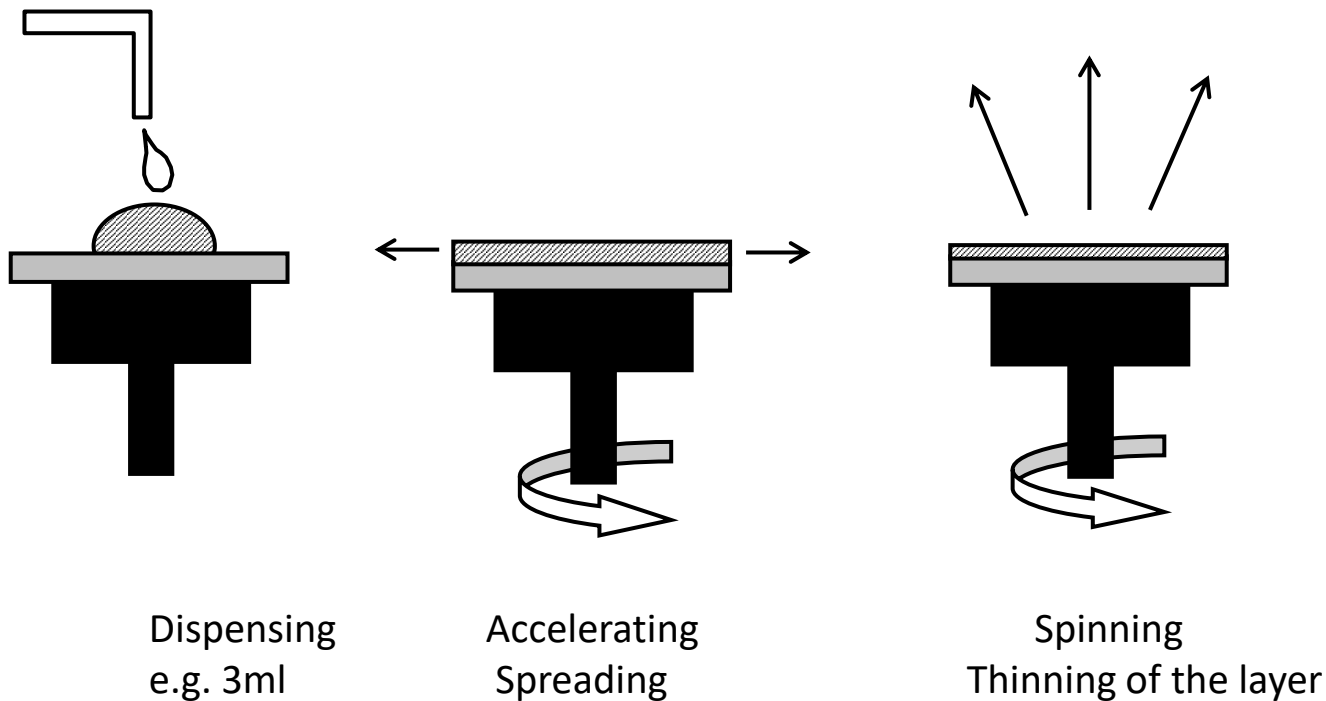
SU-8 neuron growth scaffold

Fabrication of SU-8 channels

Any substrate material

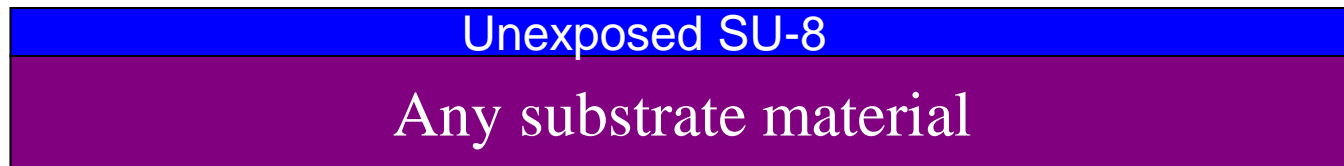
SU-8 spinning

Viscosity and spinning speed determine thickness,
for example, 20 μm thick SU-8 layer for fluidic chip.



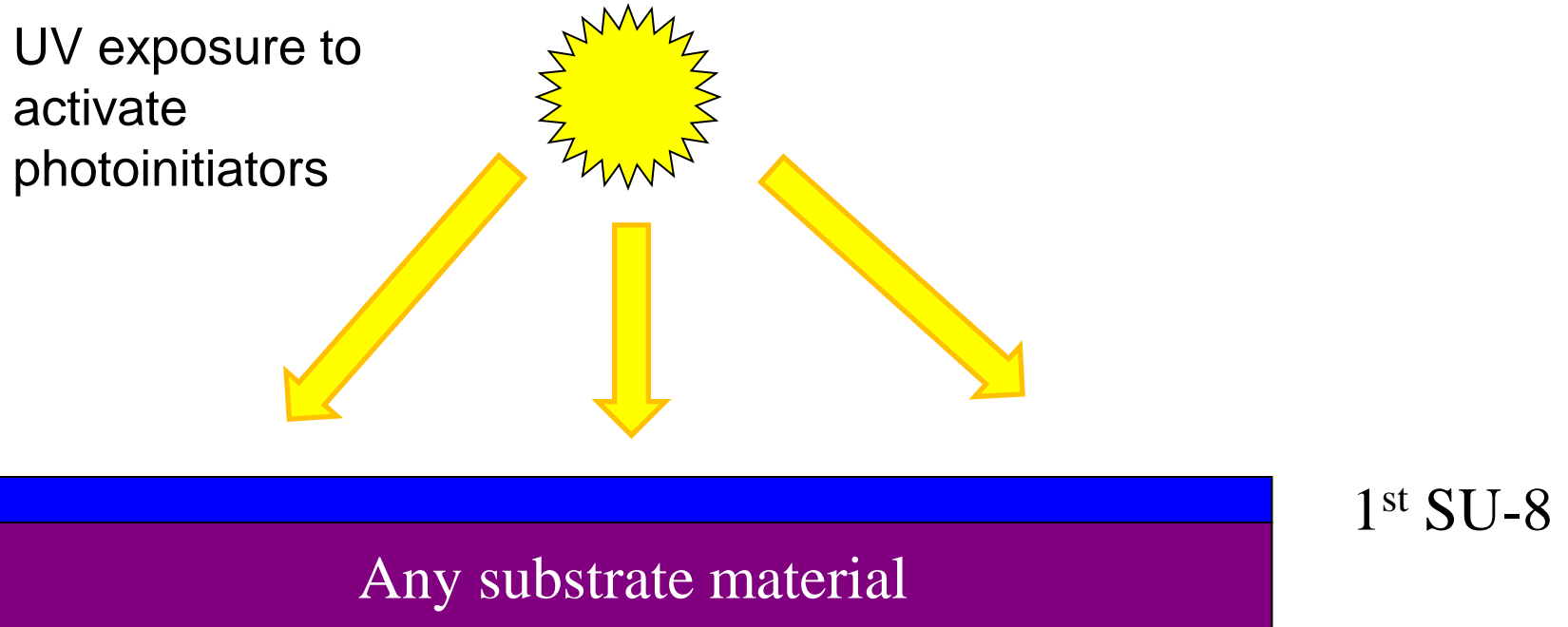
Soft bake to remove solvent

Soft bake at 95°C to remove solvent, time depends on the thickness



1st SU-8

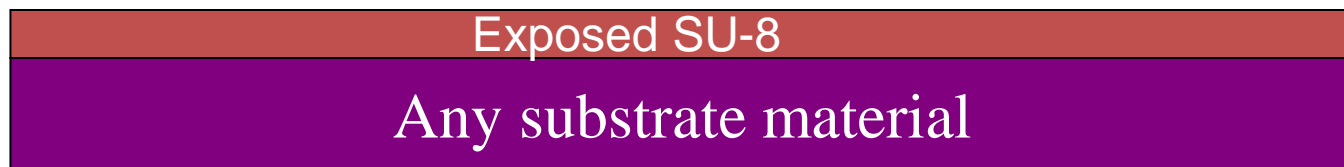
UV exposure to polymerize



Another bake to finalize polymerization

Post exposure baking at 95°C to cross link SU-8

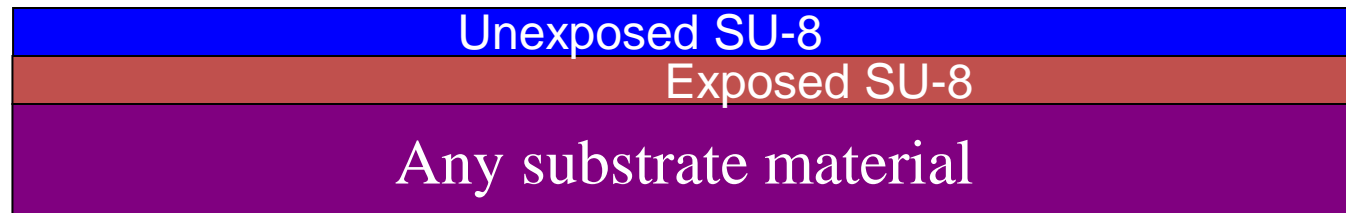
Activated photo initiators and thermal energy allow for cross linking



1st SU-8

Second layer for channel formation

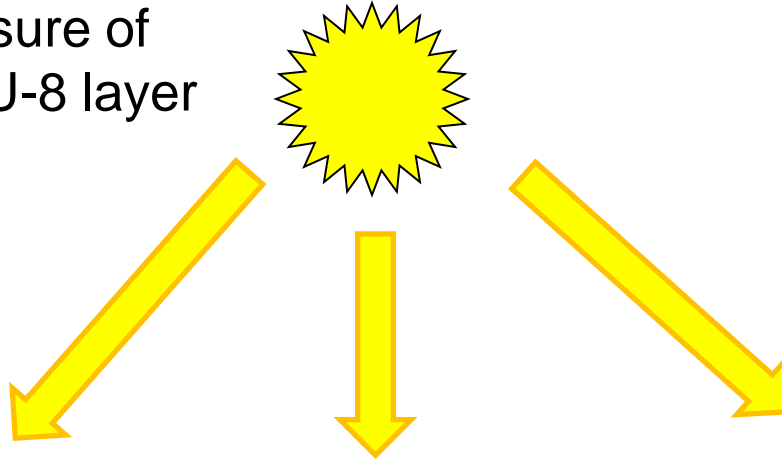
Spin coating second SU-8 layer
Soft bake at 95°C to remove solvent



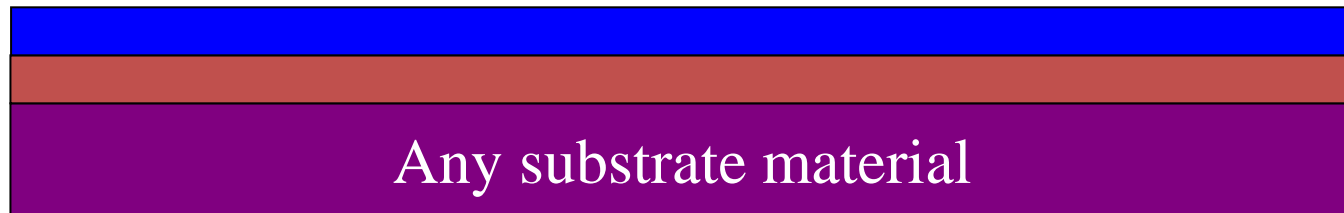
2nd SU-8
1st SU-8

UV-exposure thru a mask

Masked exposure of
the second SU-8 layer



photomask



2nd SU-8

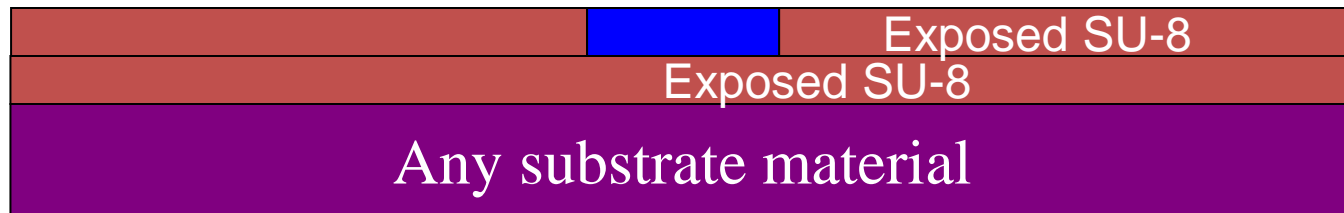
1st SU-8

Any substrate material

Another bake...

Post exposure baking at 95°C to cross link exposed SU-8

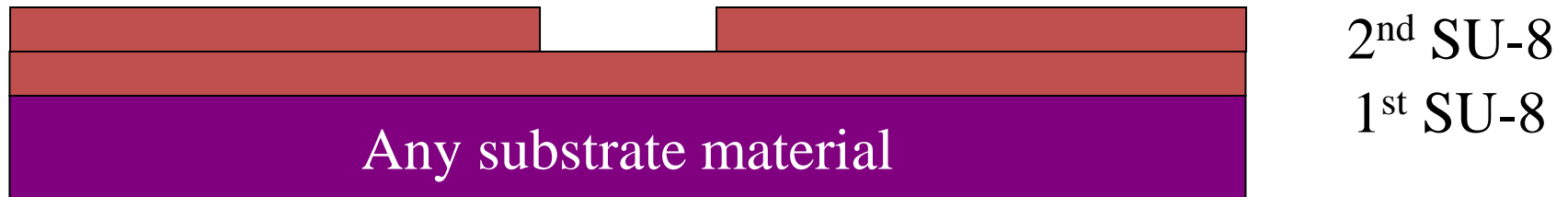
The area protected by mask does not crosslink due to inactive photo initiators



2nd SU-8
1st SU-8

Development leads to channels

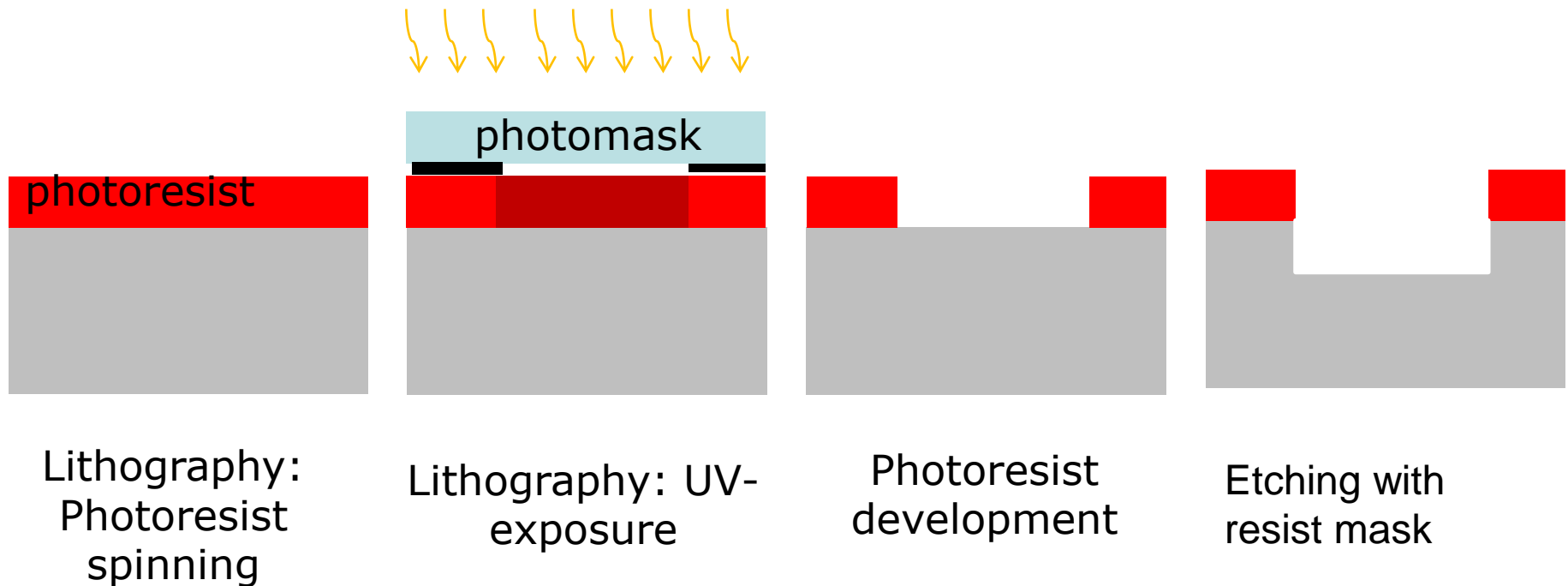
Developing the wafer in an organic solvent (PGMEA) to remove non-cross linked SU-8



Lithography + etching

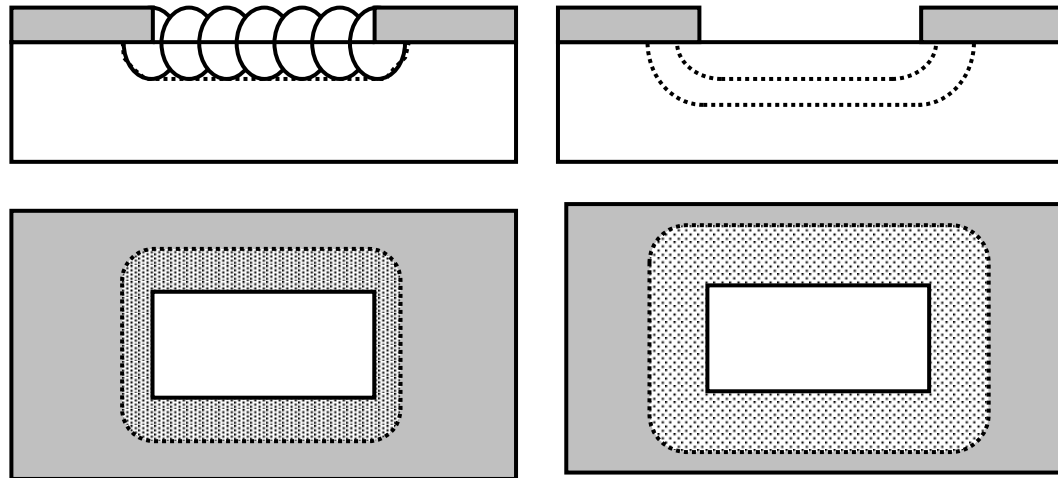
Use photoresist as a mask to etch a channel

Benefit: we can etch many materials, and we are not limited to polymers.

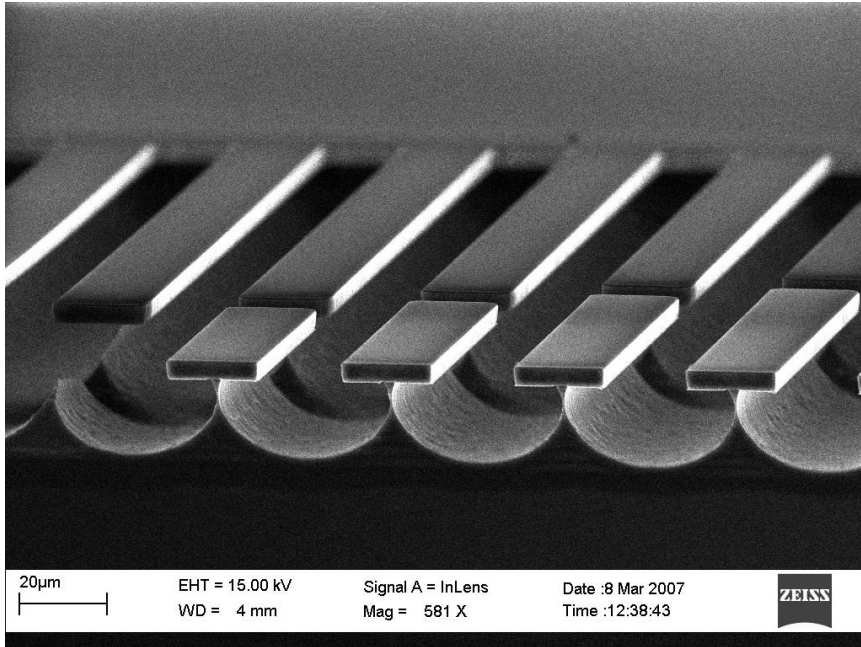


Isotropic etching

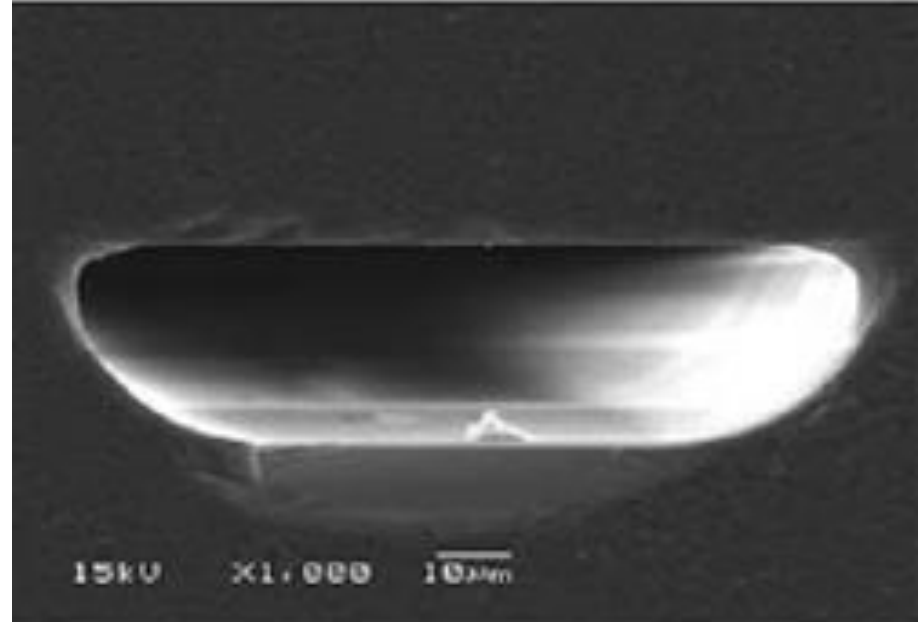
- Proceeds as a spherical wave
- Undercuts structures (proceeds under mask)
- Most wet etching processes are isotropic
- HF etching of SiO_2 and glass, H_3PO_4 etching of Al



Isotropic etch profiles

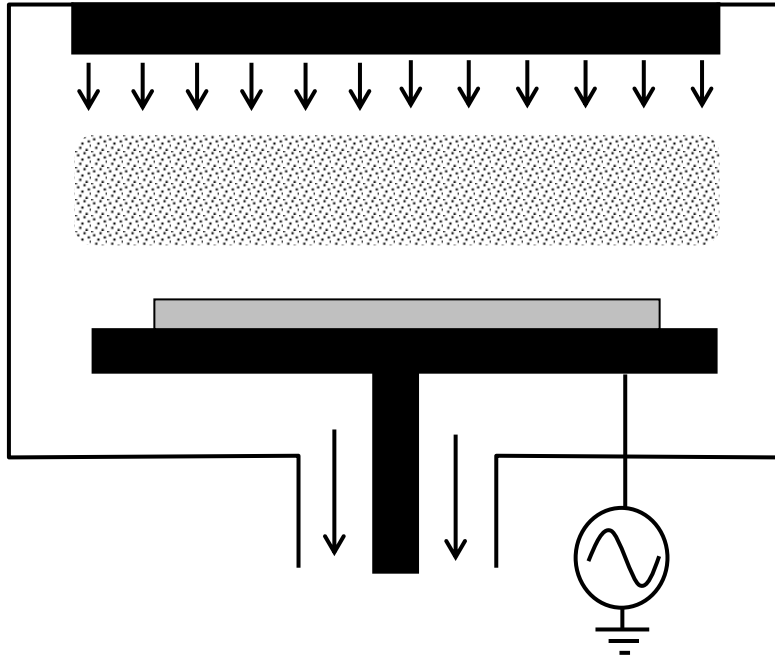


Silicon etched in isotropic SF_6 high pressure plasma



Glass wafer etched in HF (with roof bonded)

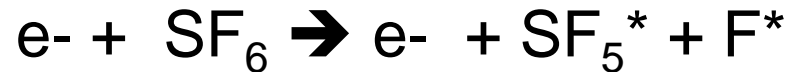
Plasma etching/RIE



vacuum 1 mTorr-3 Torr

13.56 MHz RF

SF₆ feed gas to etch silicon:



Reactive neutrals very reactive

→ High etch rate

Ions provide directionality

→ vertical walls

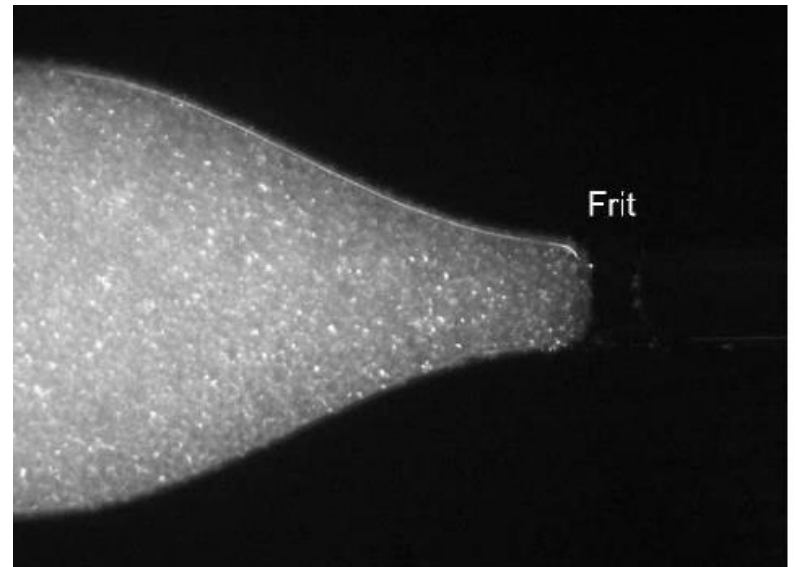
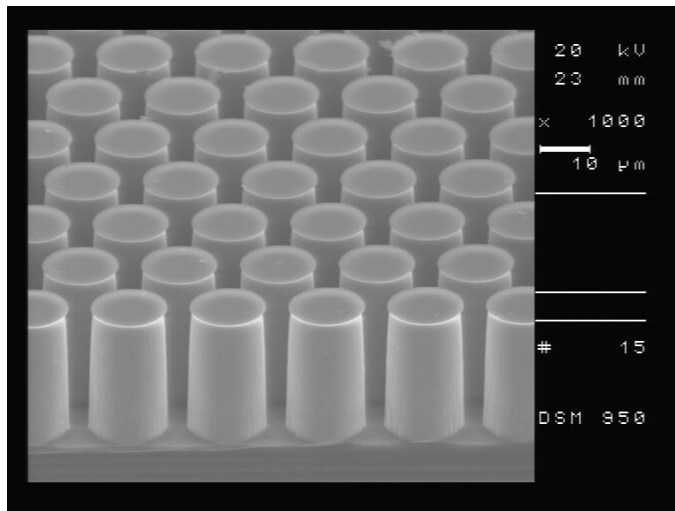
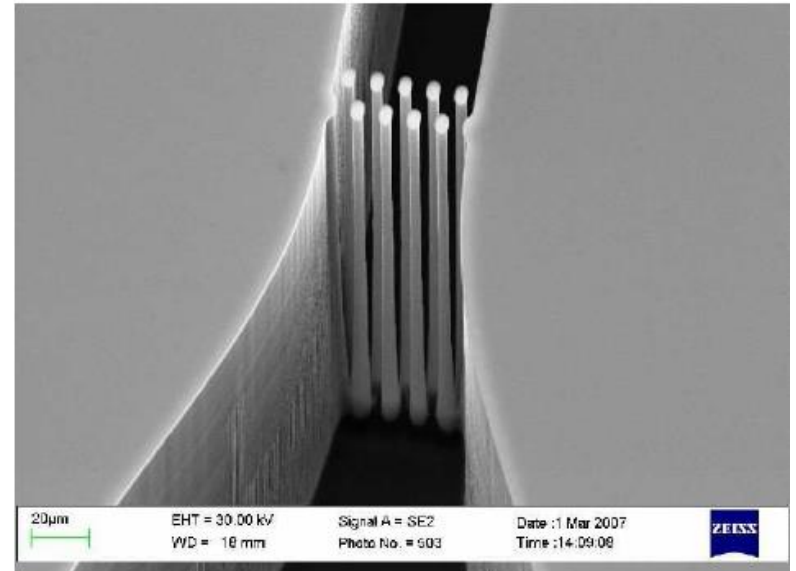
Note 1: RIE = Reactive Ion Etching = plasma etching

Note 2: ions have minor role; excited neutrals major

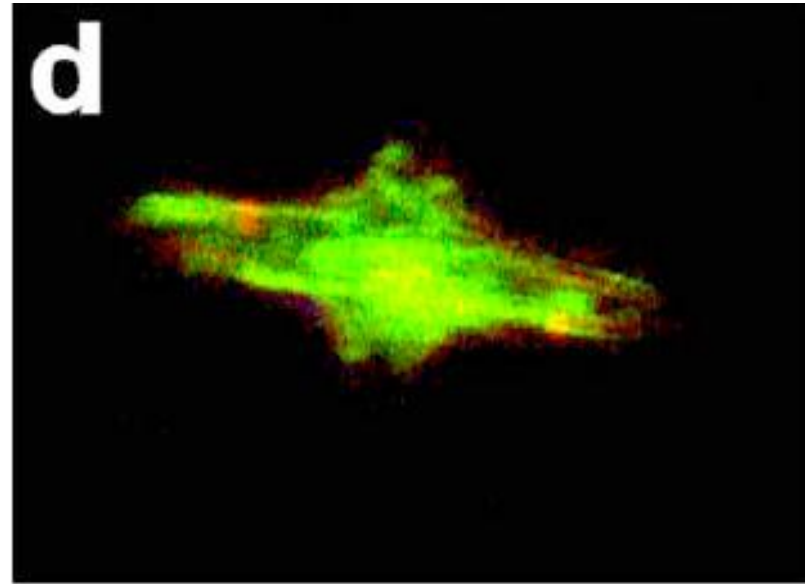
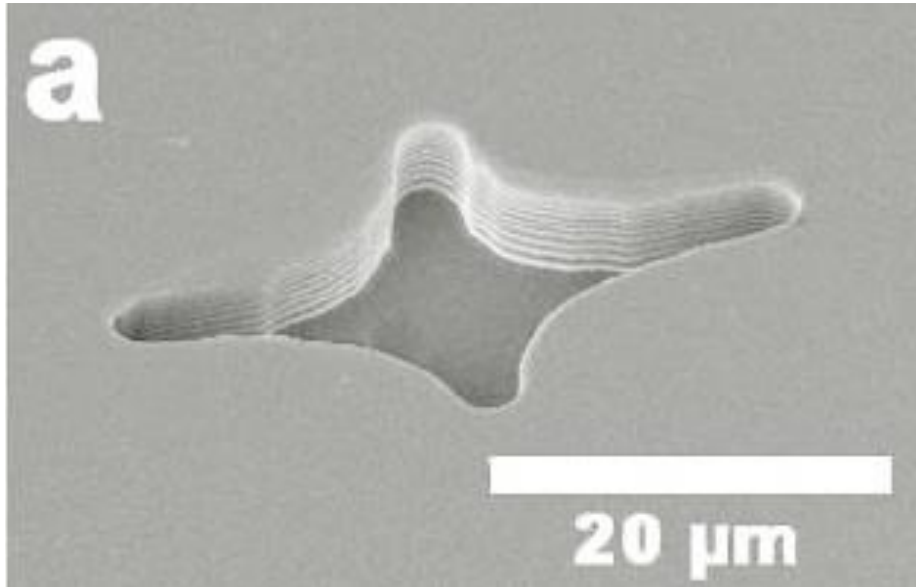
Plasma etching of silicon

Possibility to make
vertical walls

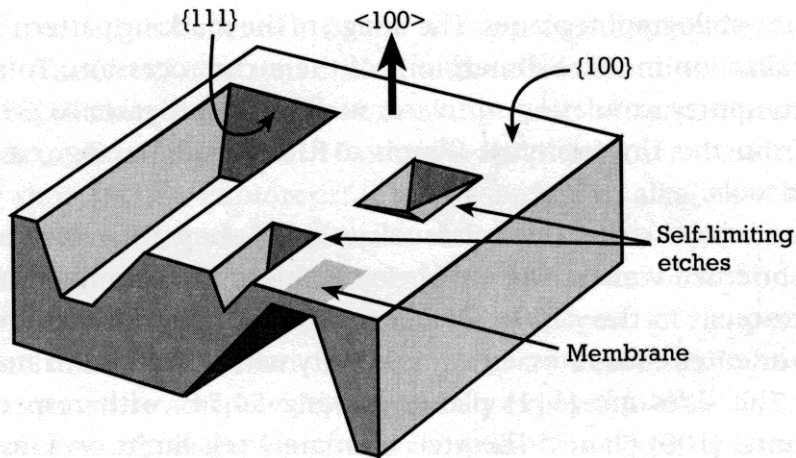
→ narrow gaps



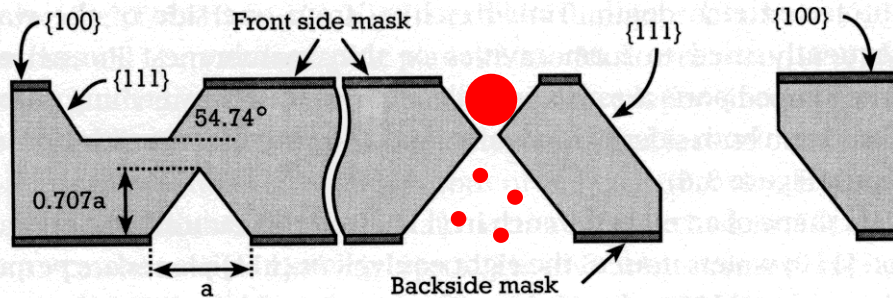
Cell growth forced into arbitrary shapes formed by plasma etching



Alkaline etching of silicon



(a)



(b)

(100) and (110) crystal planes etch fast: 1 $\mu\text{m}/\text{min}$ typical

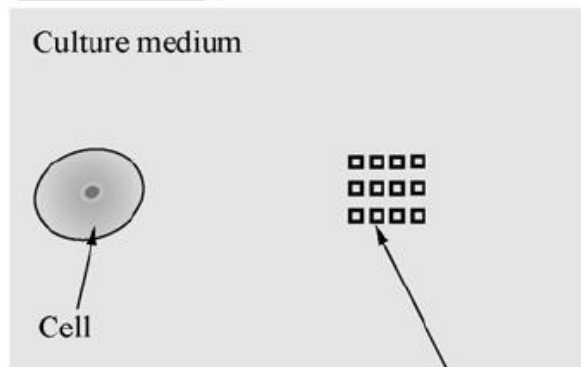
(111) plane etches slow, 10 nm/min typical

Uses SiO_2 as etch mask

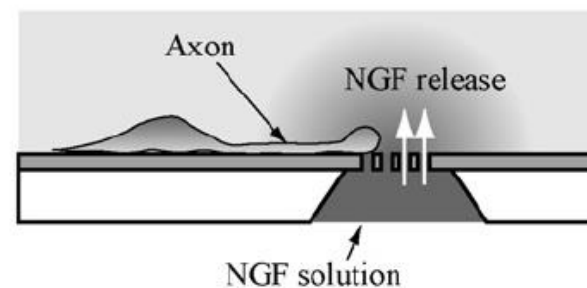
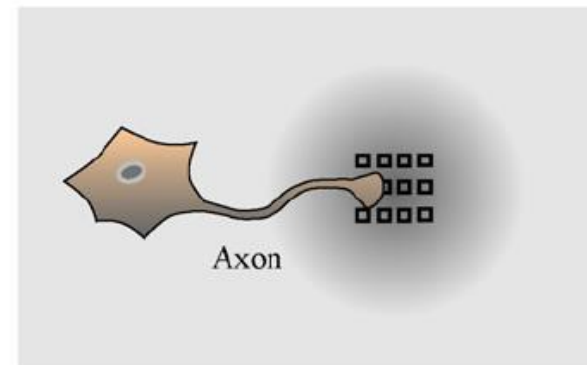
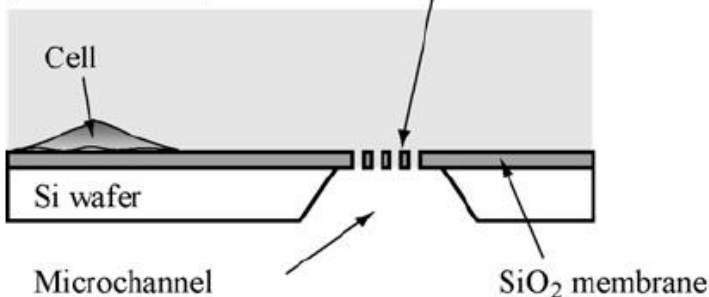
(photoresist and oxide etching is used to make patterns in oxide, and this is immersed in KOH)

Cell growth stimulator: wet and plasma etching

Top view



Side view



Three ways to etch silicon

Isotropic wet etching:

- easy and fast
- not suitable for small structures

Plasma etching:

- when vertical walls are needed
- when small structures are needed

Alkaline wet etching:

- crystal plane defined shapes
- only applicable to silicon

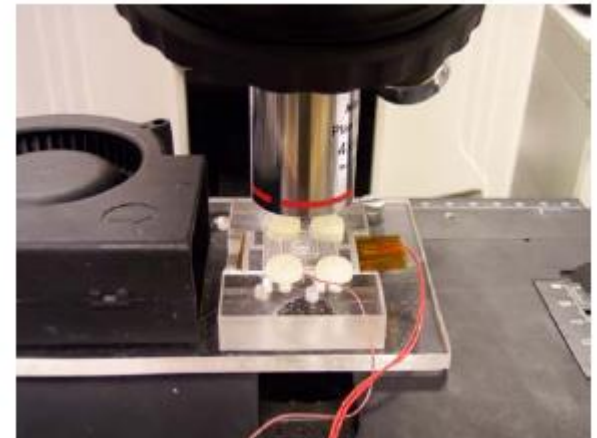
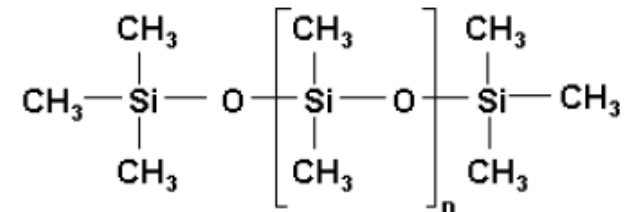
Fabrication example 2: PDMS by replication molding

PDMS elastomer is the most widely used polymer for microfluidics

- Very easy to fabricate by casting
- Non-toxic
- Excellent optical properties
- Thermally stable but huge CTE
- Ease of sealing and bonding
- Permeable to O₂ and H₂O (not always positive)

Problems:

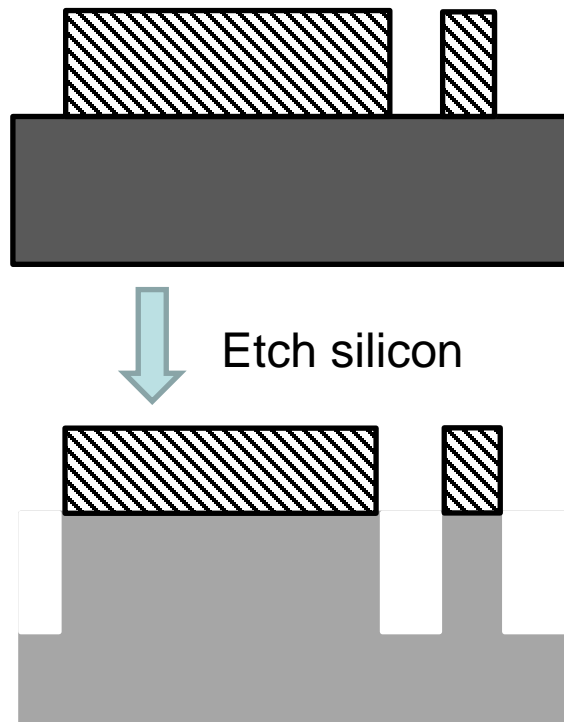
- Hydrophobicity
- Poor solvent compatibility
- Elasticity (sometimes)



PDMS PCR chip

PDMS replica moulding

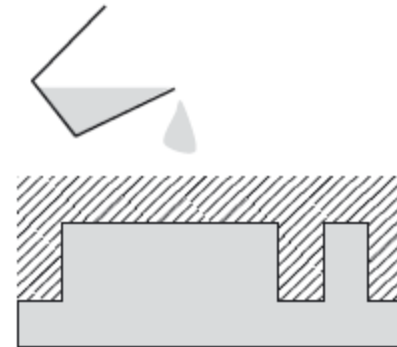
Lithography as usual,
resist patterns.
Use resist directly, or etch
into silicon.



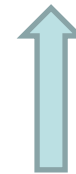
Use SU-8
as master



Then casting liquid
PDMS prepolymer on
your pattern



Use silicon as
master

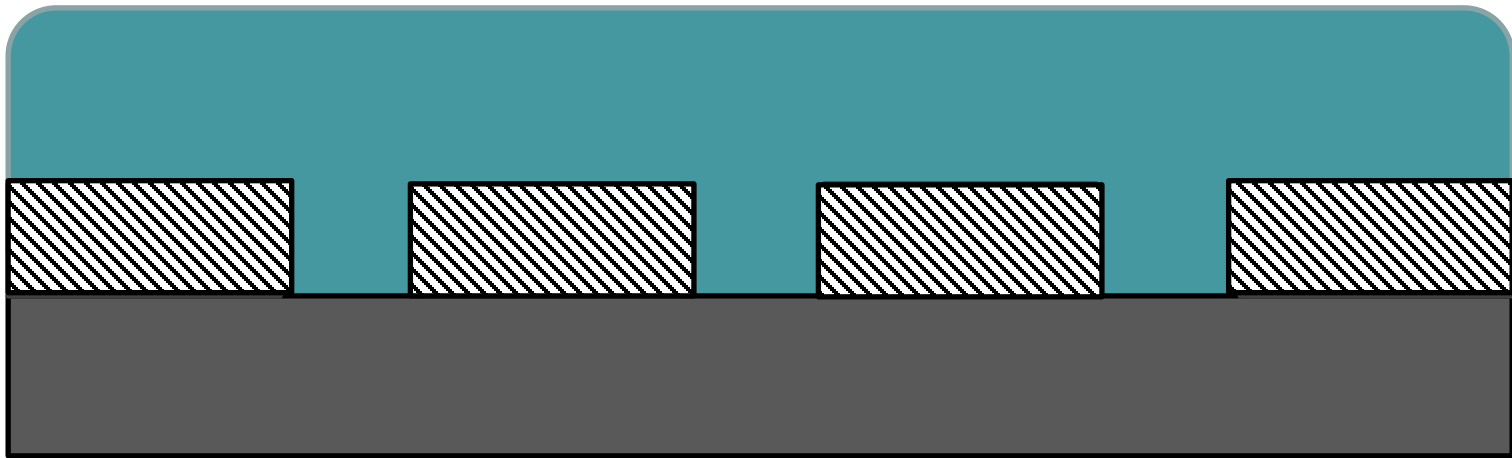


Strip
resist



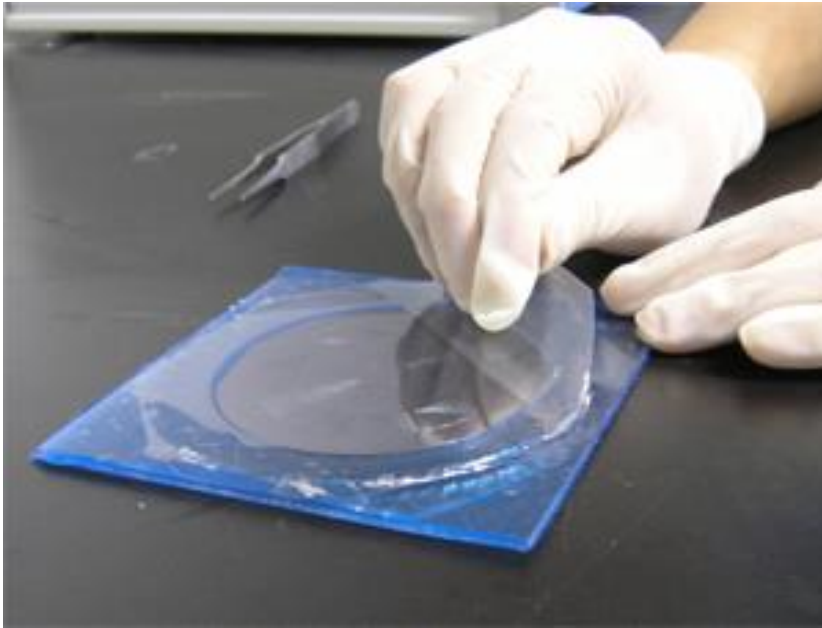
PDMS replica moulding (2)

- PDMS crosslinking by thermal activation.



- Possible curing times e.g.
 - 1 day in room temperature
 - 3 hours in 50°C
 - 1 hour in 90 degrees

PDMS properties



Peeling from master
mould

Elastic

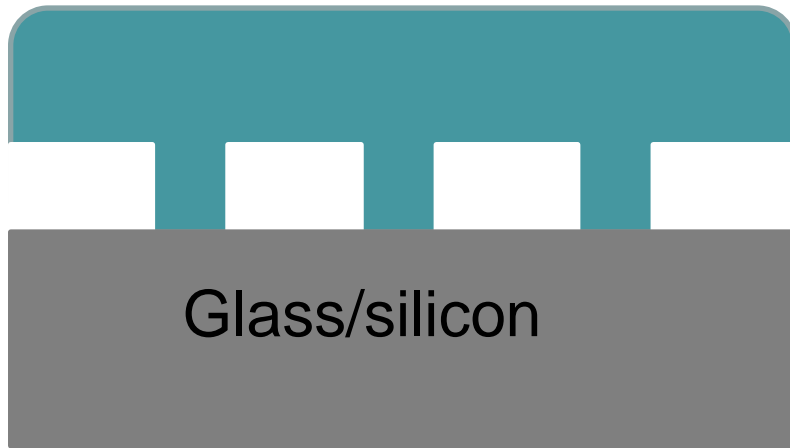
→ peeling easily from
master wafer

Transparent

→ optical detection

OK with fluids of biological
interest (water-based); but
adsorption may be a
problem

PDMS properties (2)



Bonding to a silicon wafer

Self-adhesive

→ bonding to a clean wafer

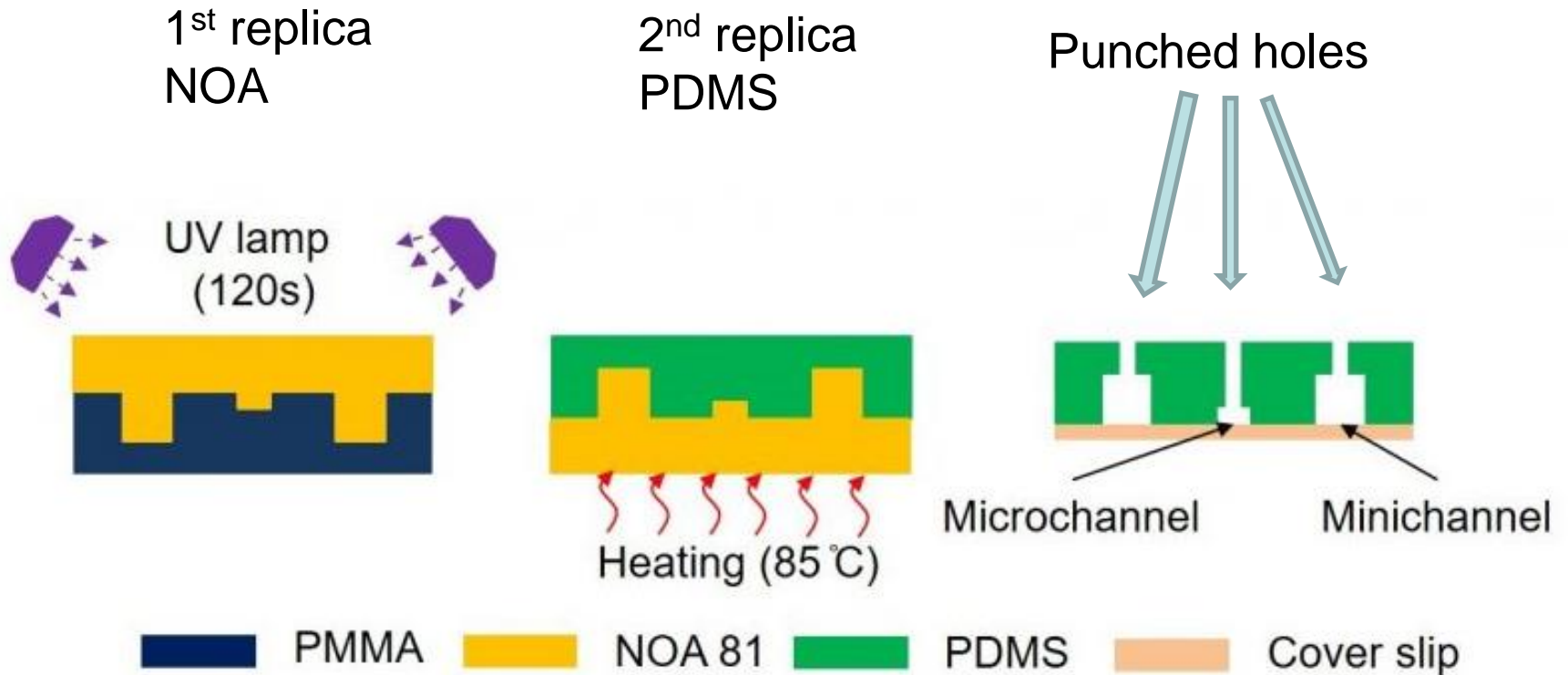
Soft

→ makes intimate contact even with a rough surface

Water vapor and oxygen permeable

→ cells can breathe under PDMS (but water will escape if system is heated)

Double replication



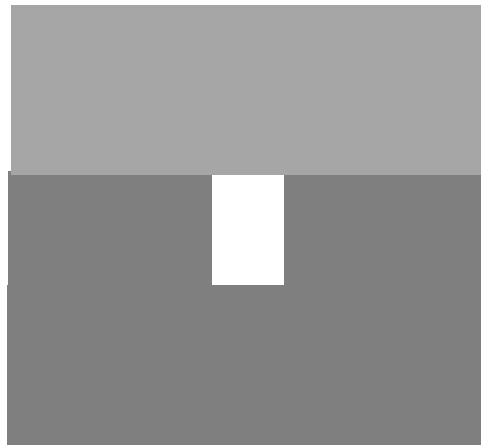
NOA= Photoactive polymer

Channels by bonding

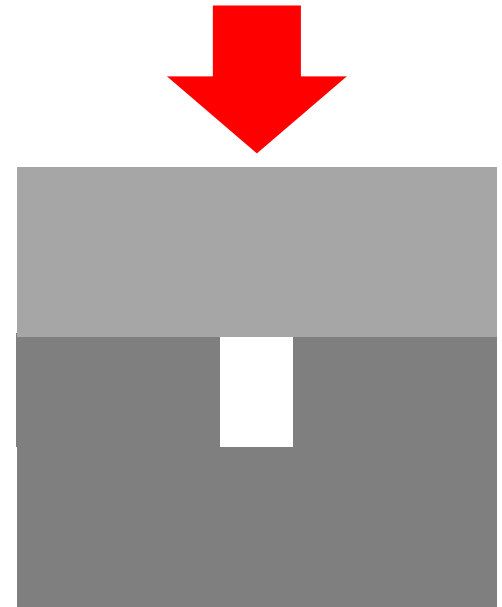
Ensure flatness
and smoothness



Clean the surfaces
1) Particle removal
2) Surface
chemistry



Join the wafers
(at room
temperature)

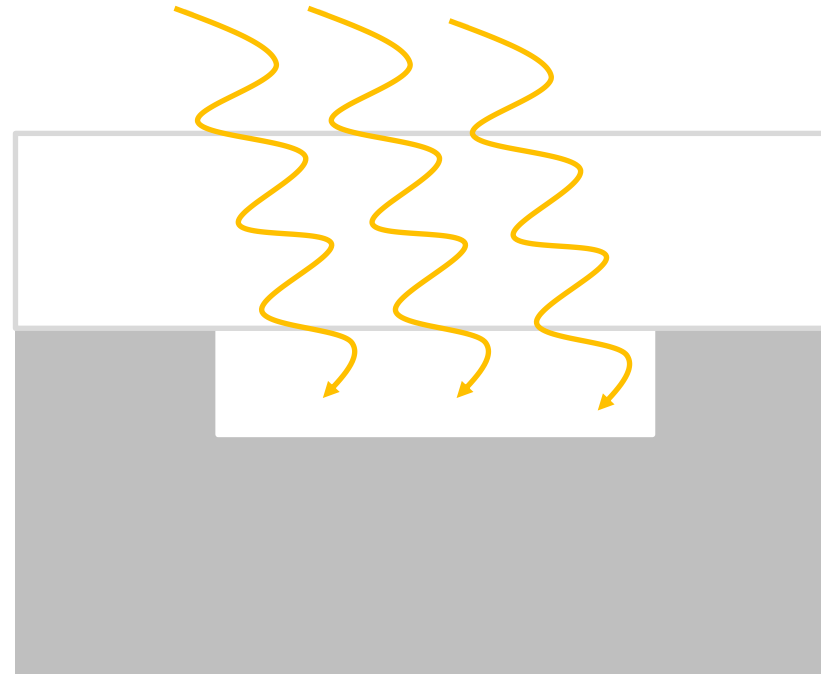


Apply force
(pressure, heat,
voltage) to
strengthen the
bond

Etched channel + bonded roof



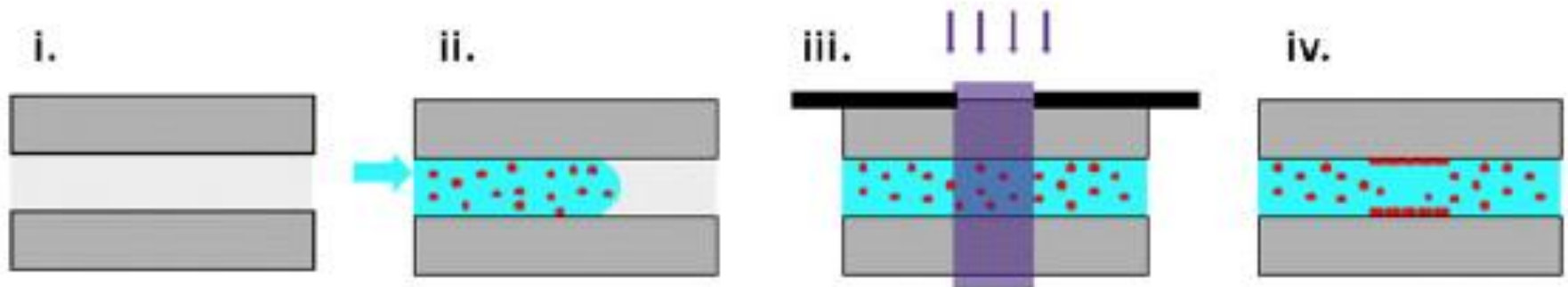
- more permanent materials
(e.g. silicon instead of polymer)
- fewer materials



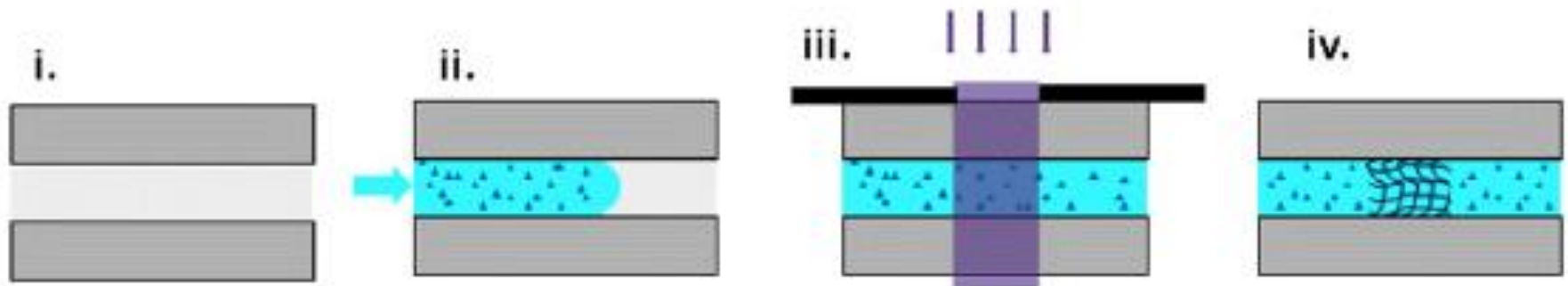
- transparent roof
- dielectric material
(depends if an electrical device)

Patterning inside microstructures

(A) Modifications to Channel Surfaces by Photopatterning



(B) Creation of Structures in Channel Volumes by Photopatterning



Direct/thermal bonding

Two identical materials bonded:

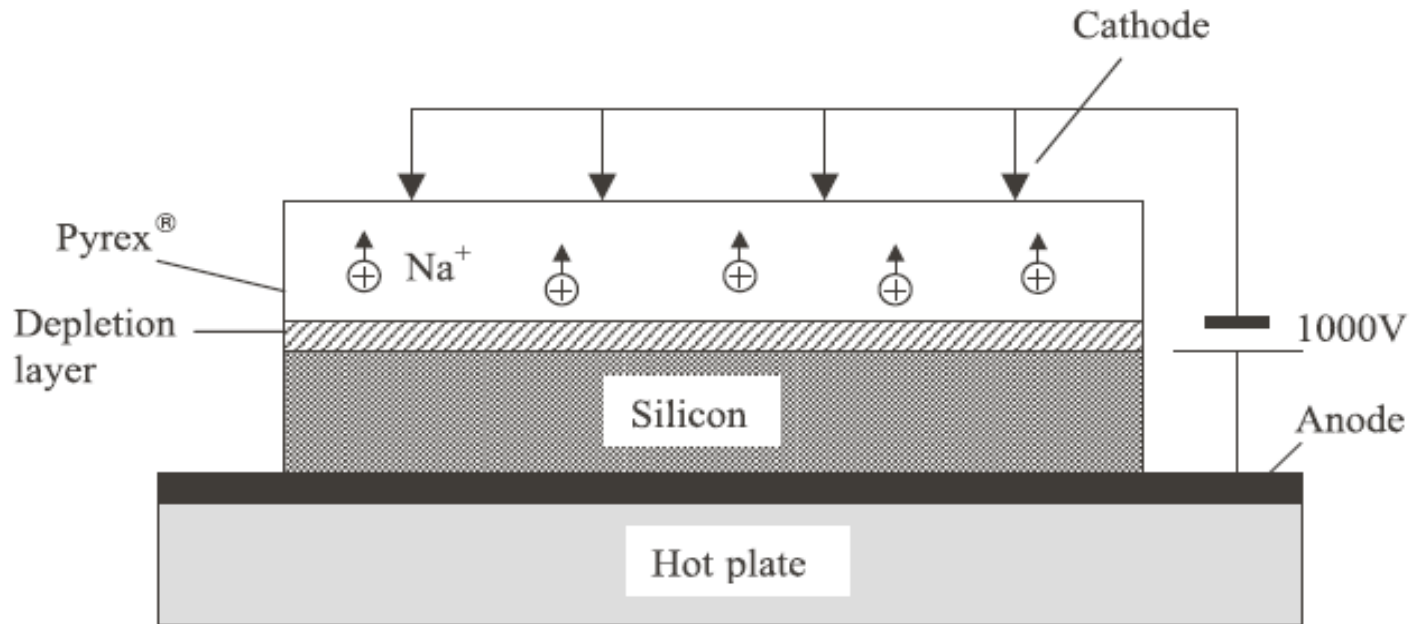
- silicon-to-silicon ca. 1000°C
- glass-to-glass ca. 600°C
- polymer-to-polymer ca. 100-200°C

Polymer thermal bonding

Raise temperature above T_g

- ➔ softening
- ➔ intimate contact
- ➔ cool down below T_g
- ➔ bond interface indistinguishable from bulk materials (because same bonds !)

Si-glass anodic bonding

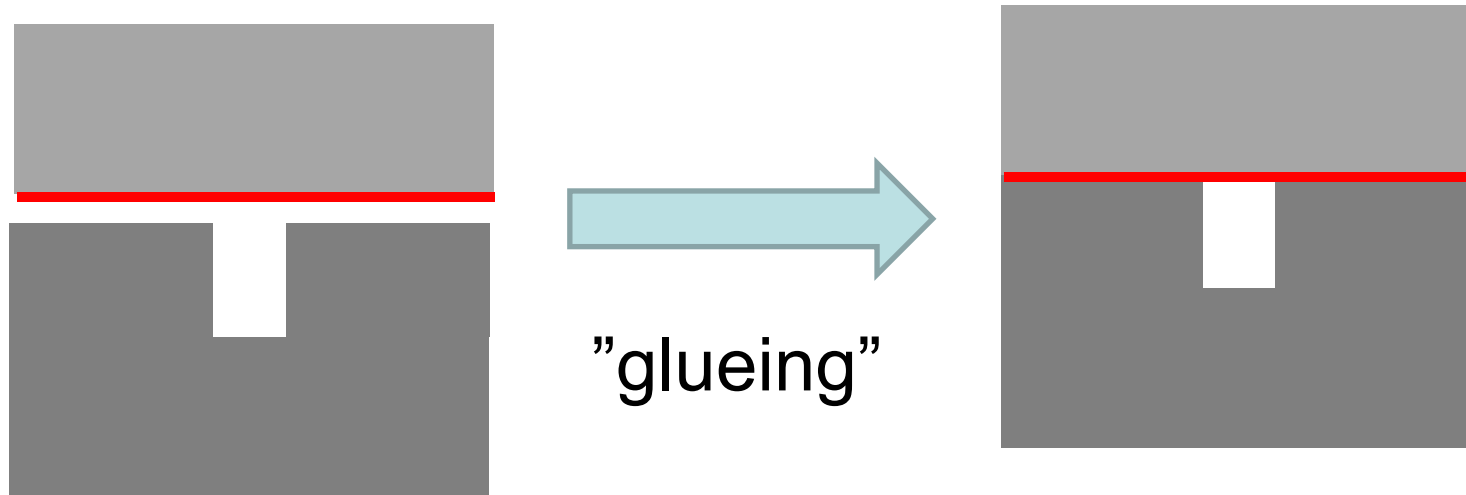


Double Sided Heating: **e.g. 350°C**

High Voltage: **e.g. 500V**

Bonding Atmosphere: **e.g. 1 mbar nitrogen**

Adhesive bonding



- any two materials can be joined by polymer interlayer
- glue remains in the structure, and may react with chemicals
- temperature is ca. 100-200°C only
- no pressure needed

Bonding of SU-8 channels

Start of the bonding process.

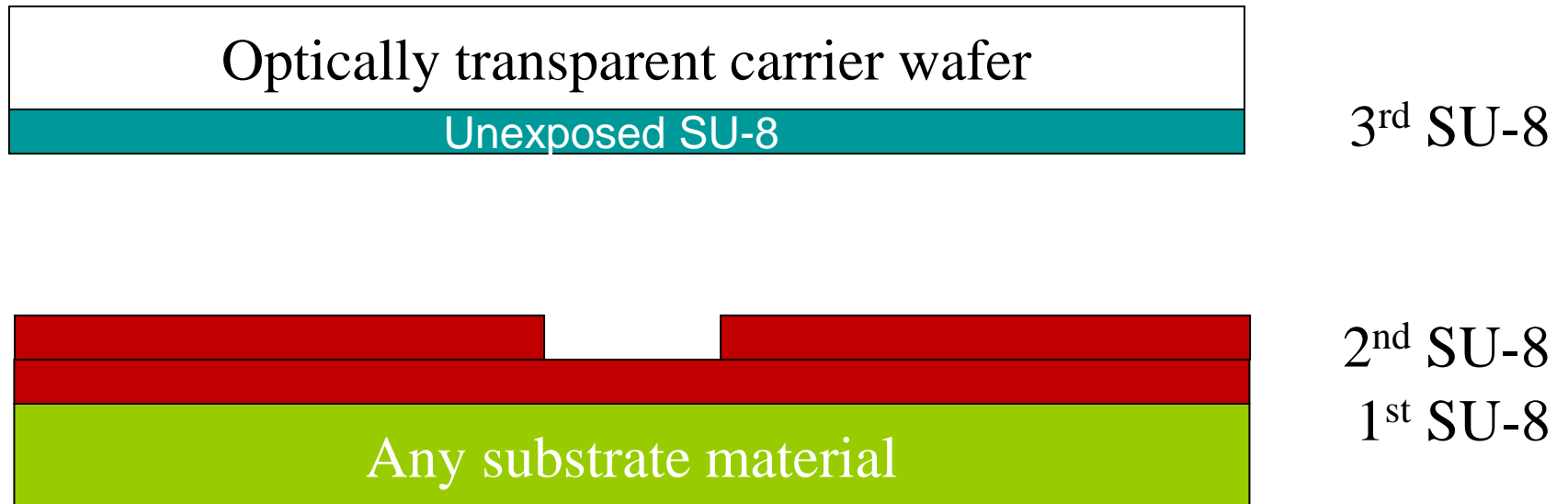
Spin coating a SU-8 layer on top of a temporary transparent substrate

Soft bake at 95°C to remove solvent



3rd SU-8

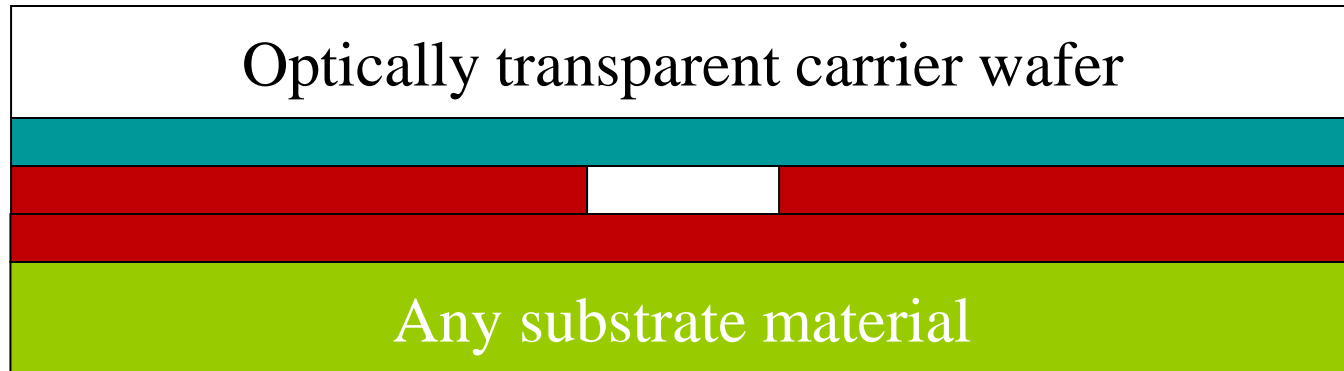
Carrier wafer with adhesive layer



Preliminary bonding @ RT

Bonding a cover lid which has an unexposed SU-8 layer

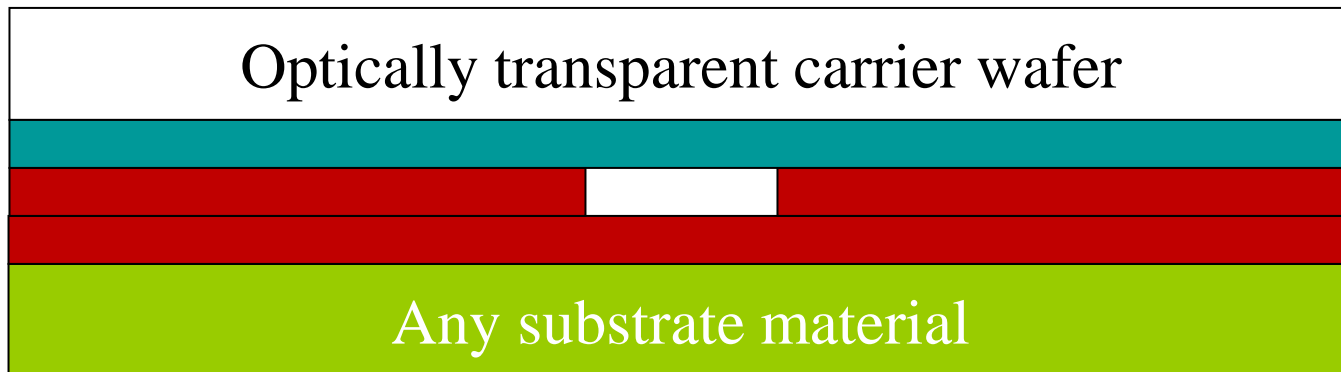
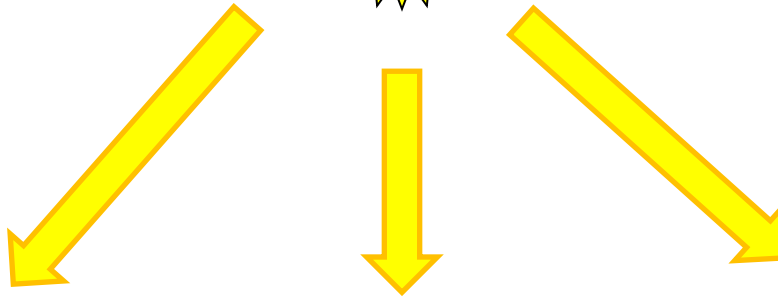
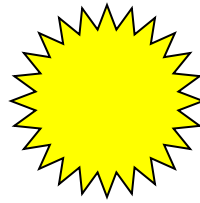
This is adhesive bonding (with thermal extra energy)



3rd SU-8
2nd SU-8
1st SU-8

UV-exposure thru carrier wafer

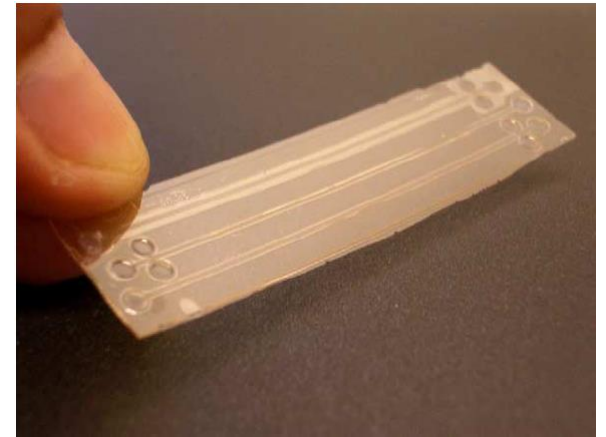
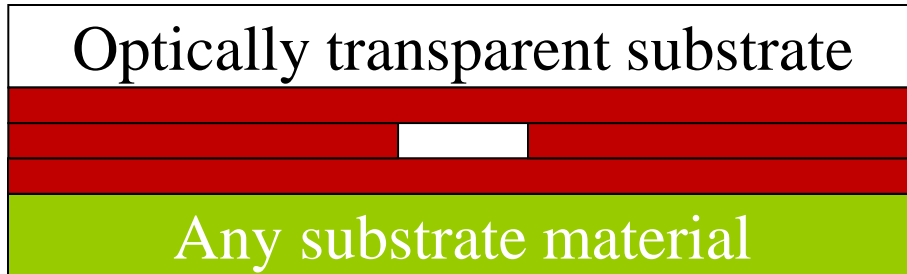
UV exposure to
activate photoinitiators
for bonding



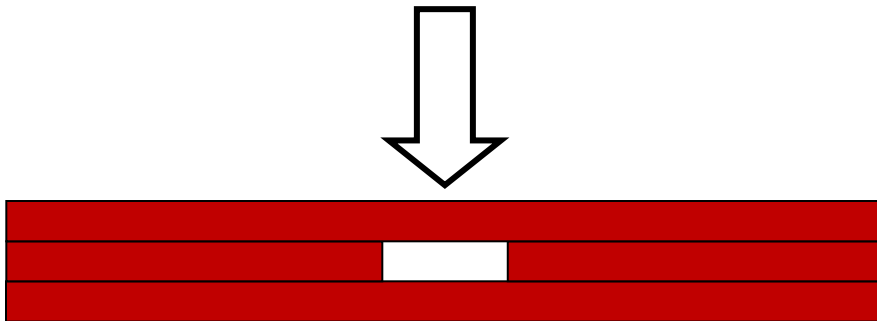
3rd SU-8
2nd SU-8
1st SU-8

Final curing of exposed SU-8

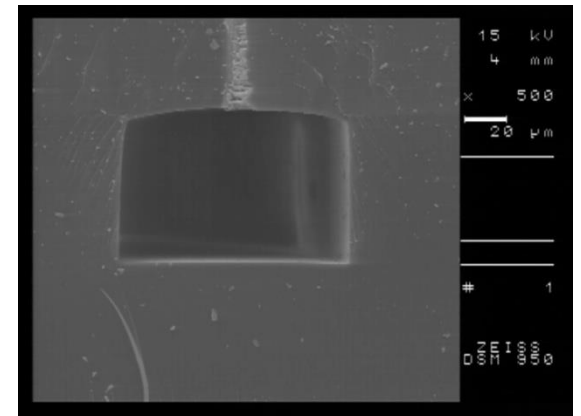
Post exposure bake to complete the bonding



Removing the substrates (optional)



Freestanding SU-8 microchip

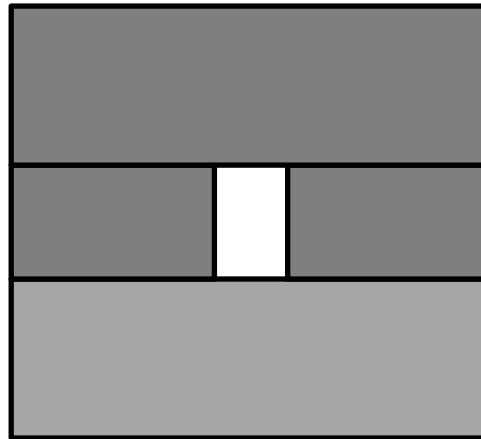


Number of materials

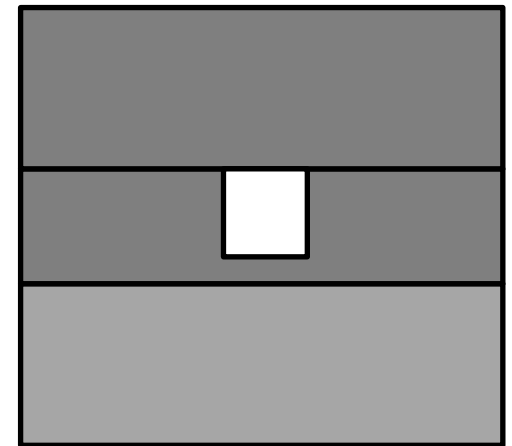
Substrate, wall and cap
→ 3 different materials



Walls and cap identical
→ 2 materials



Floor, wall and cap
same material
→ only 1 material



Wetting, charging, adsorption... easier to control if we have fewer materials present.

Channel considerations

Materials

- silicon (semi)conducting, opaque
- glass (insulator), transparent
- polymer (insulator), transparent or opaque

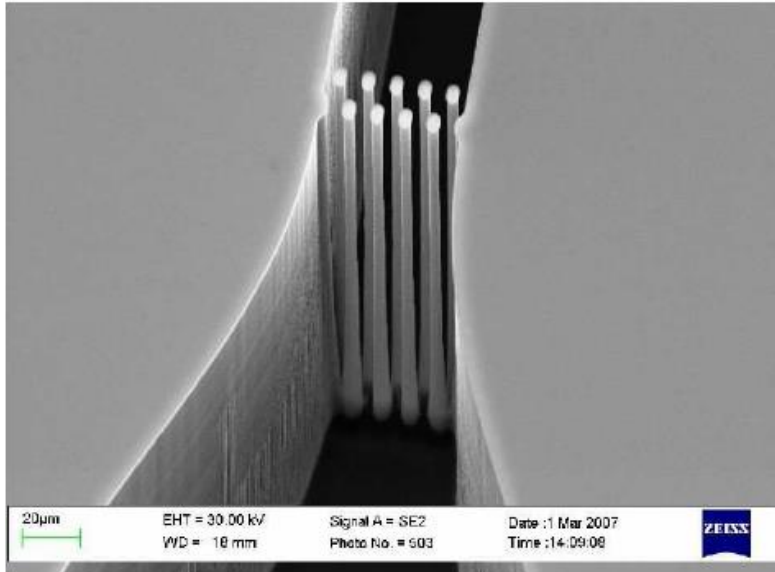
Channels

- vertical/round/slanted
- smooth/polished/textured/porous
- surface charging/electric double layer
- surface-volume ratio

Fluidics

- wetting/hydrophilic/hydrophobic
- self-filling/capillary forces
- flow dynamics/Reynolds number
- size effects/diffusion
- thermal effects/Fourier number

Lithographically defined sieve

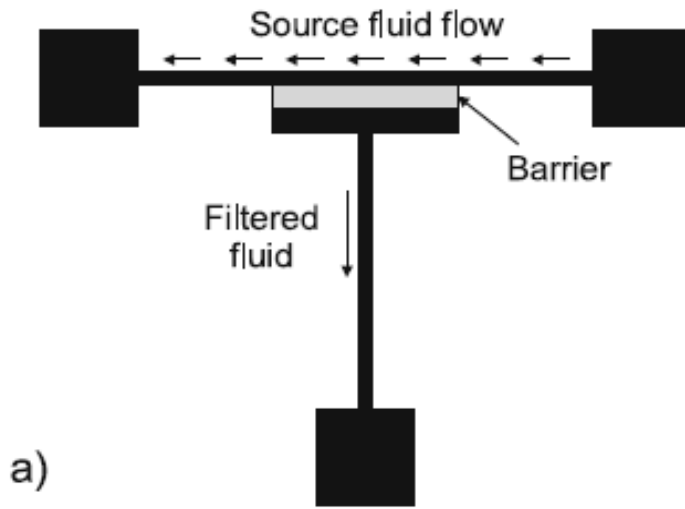


Sieve fabricated by lithography and plasma etching.

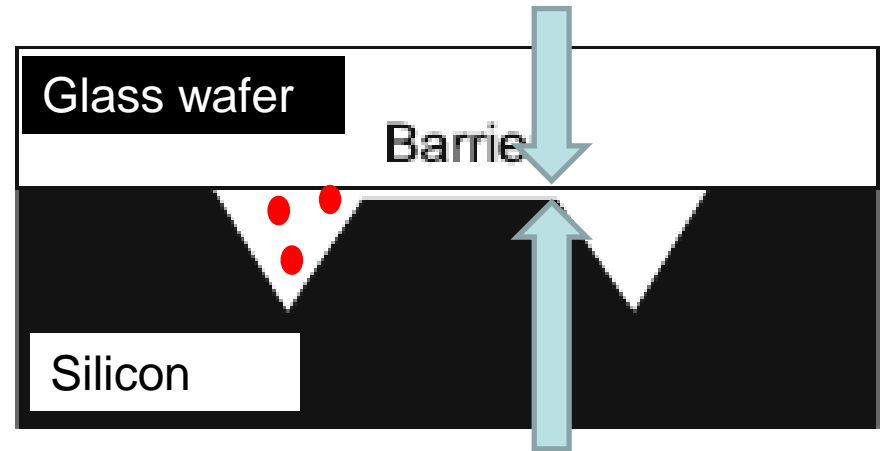
Sieve pass size determined by lithography capability.

1 μm pass size very expensive.

Bonded sieve



1 μm pass size for a bonded sieve is piece of cake.
100 nm is easy, too.

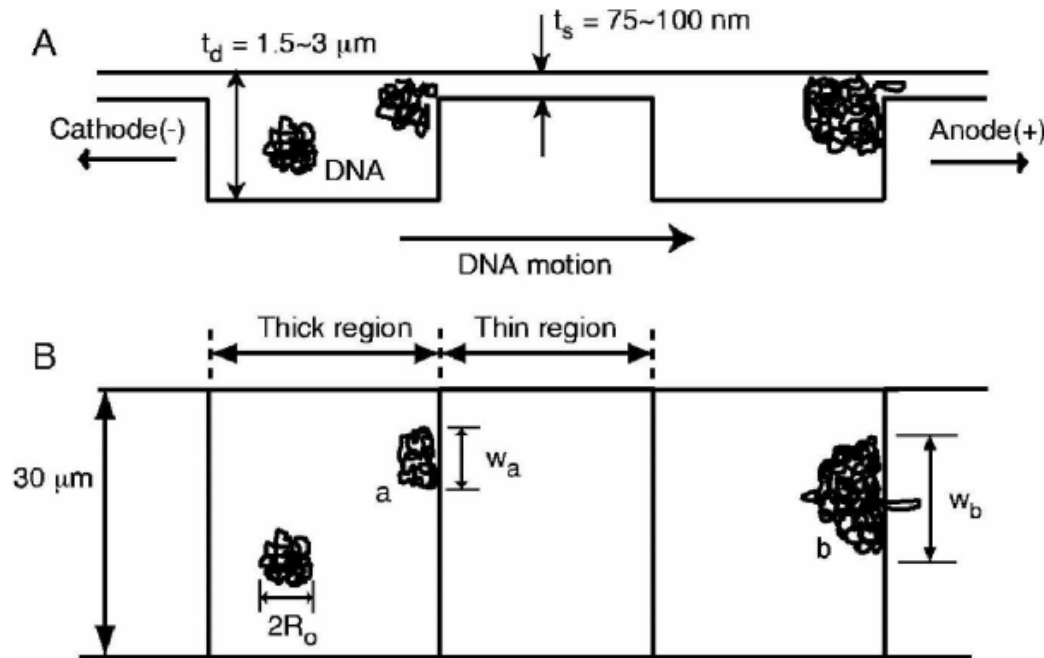


Sieve barrier height is determined by etching, not lithography

Nanofluidics:

molecular size \approx channel size

Gap size 75-100 nm easy by etching + bonding.



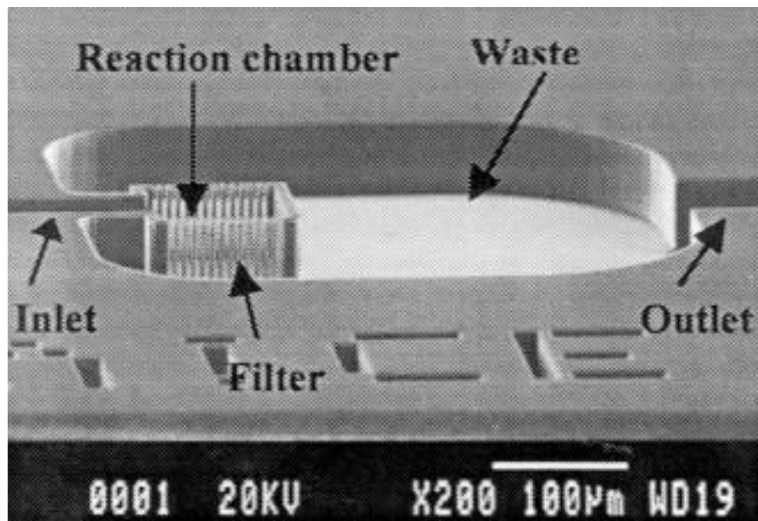
Side view

Top view

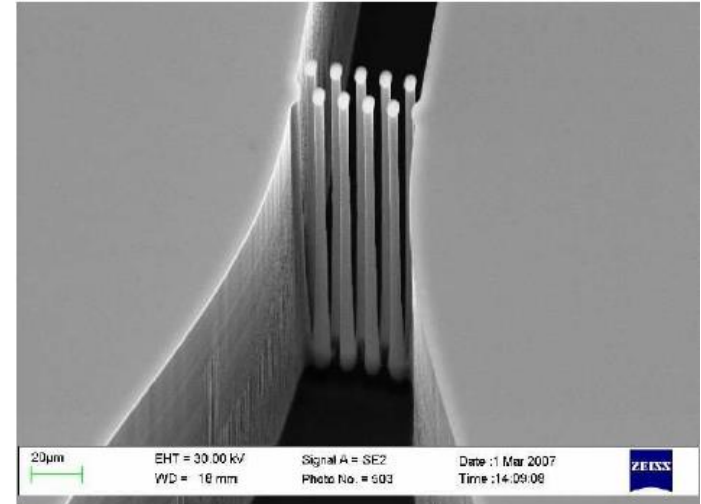
Bonding area and tightness

Bonding large areas is easier than bonding small areas.

Both must be bonded for leak-tightness.

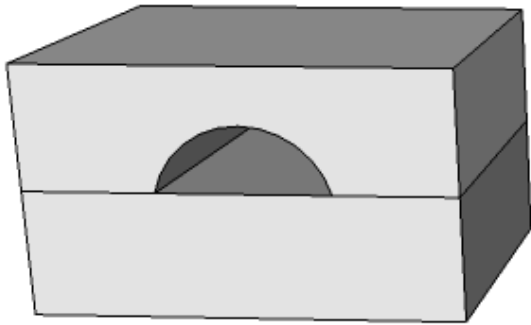


Andersson et al: Electrophoresis 2001, p. 249



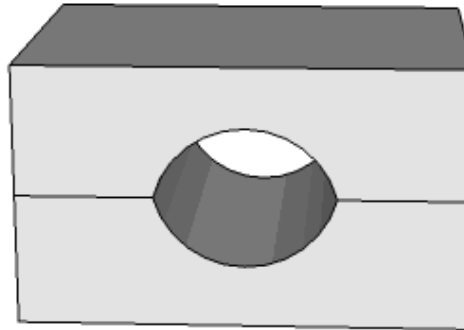
Kai Kolari, VTT

Bond alignment



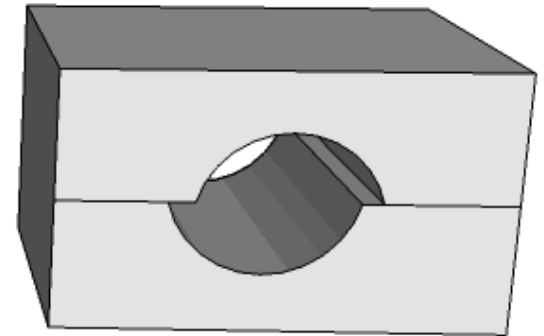
None

Simple
equipment
enough



Perfect

Requires
advanced
tools

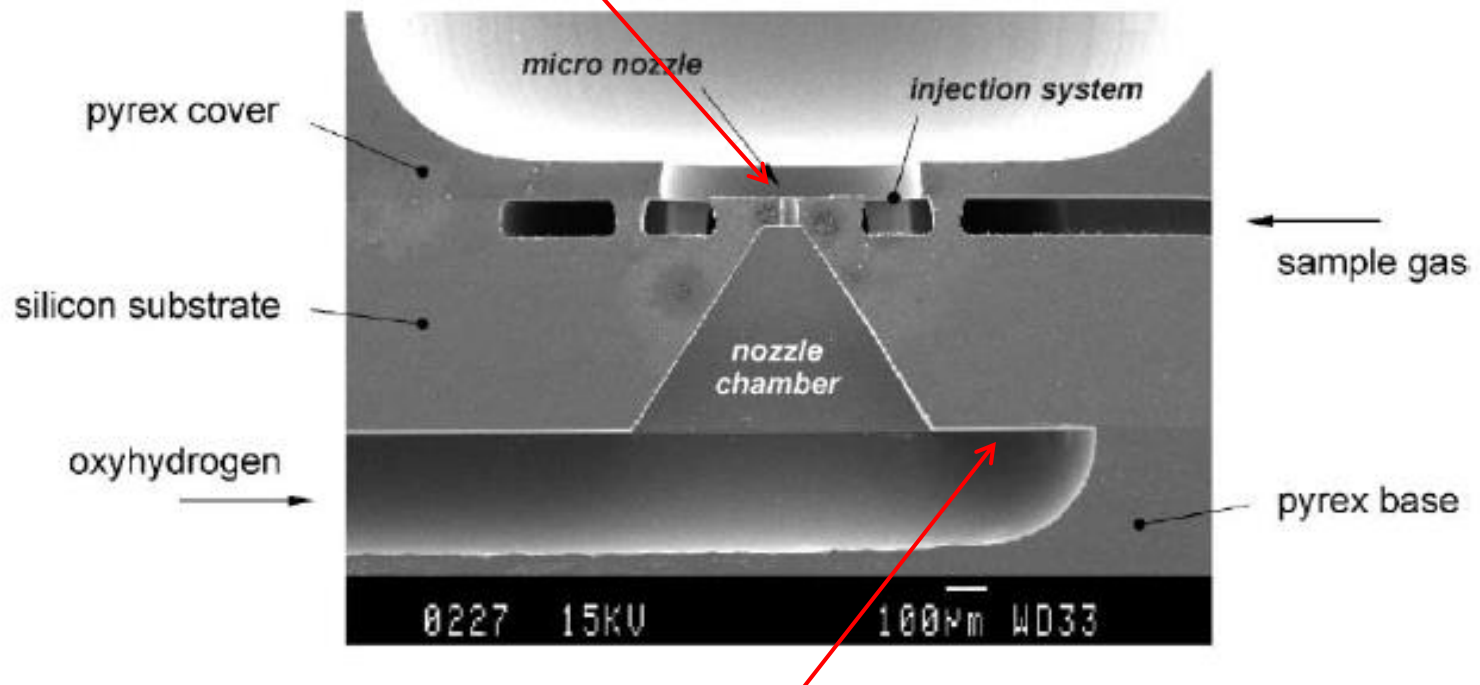


Misaligned

Some devices
more sensitive
to misalignment
than others.

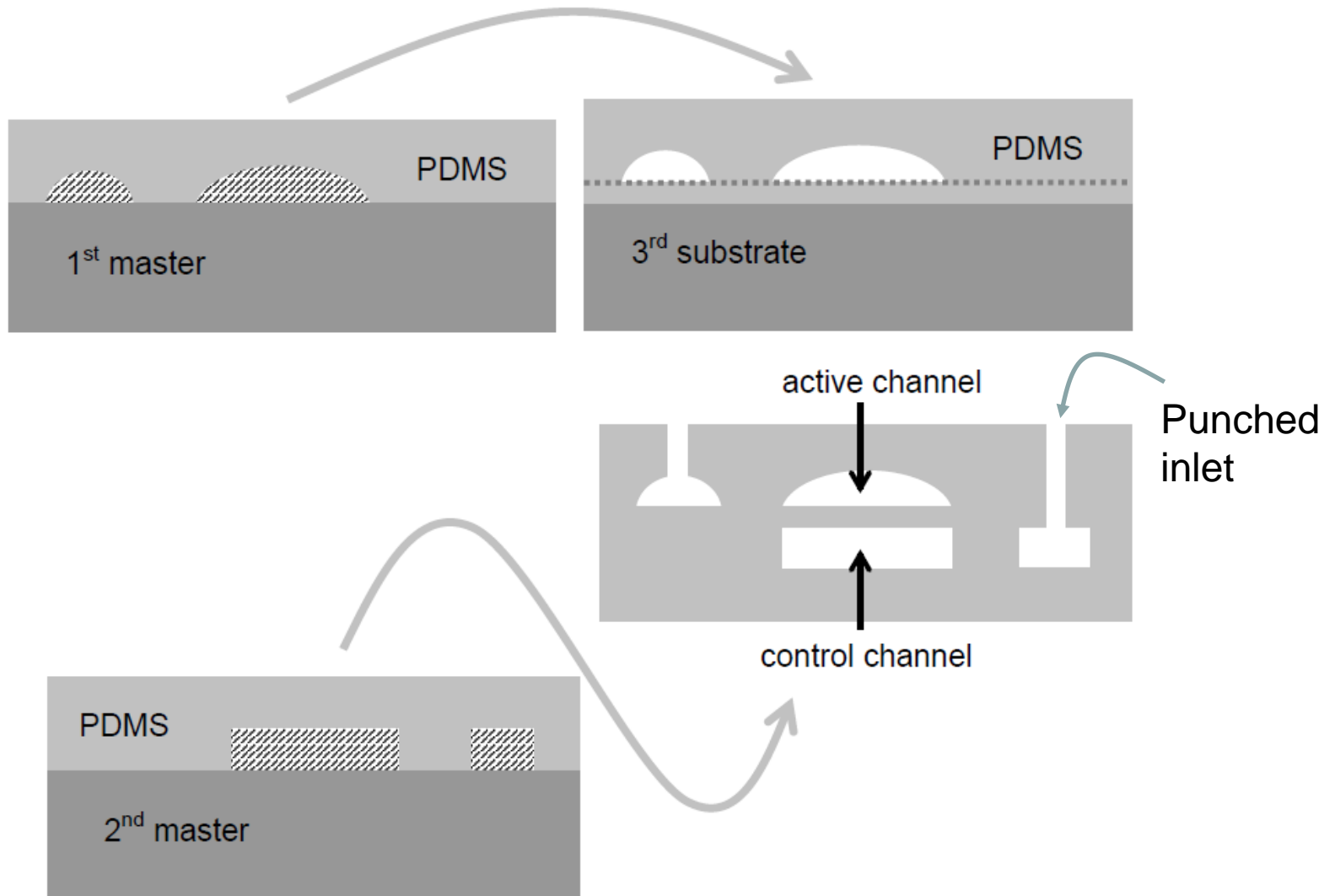
Bond alignment (2)

Critical alignment, nozzle in middle of injection system



Non-critical alignment, large volume gas reservoir

Multiple PDMS layers bonded



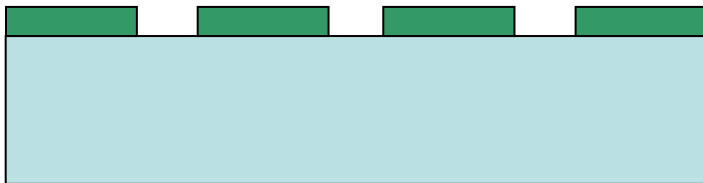
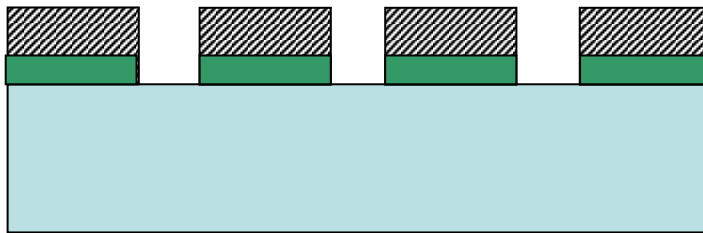
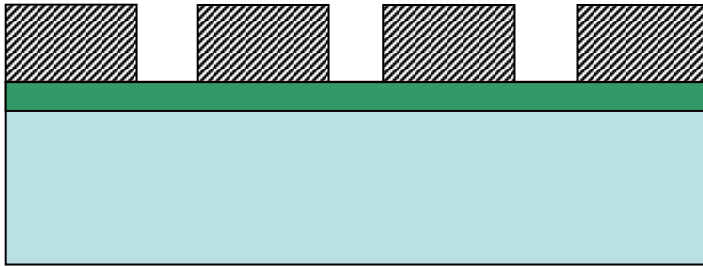
Thin films

Thin films are layers 1-1000 nm thick

They serve several functions:

- heater electrodes (W, Pt, TiN, Al, ...)
- temperature sensors (Pt)
- catalysts (Pt, Pd, ...)
- mirrors (many metals; $\lambda/4$ dielectric stacks))
- electrodes for electrical sensing (Pt, Pd, Au, ...)
- electrical isolation (SiO_2 , Si_3N_4)
- optical coatings (filters, windows, ...)
- antisticking coatings (Teflon)
- protective layers (SiO_2 , Si_3N_4 , Cr, Al, etch masks)

Thin film heater processing



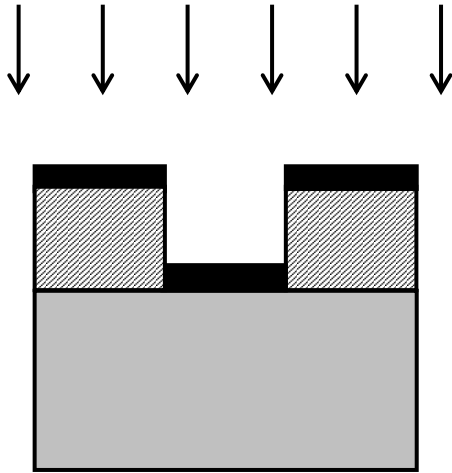
Can be done on any wafer !
Glass wafers, polymer, ...

1. Metal film evaporation
2. Photoresist spinning & baking
3. Lithography with resistor mask

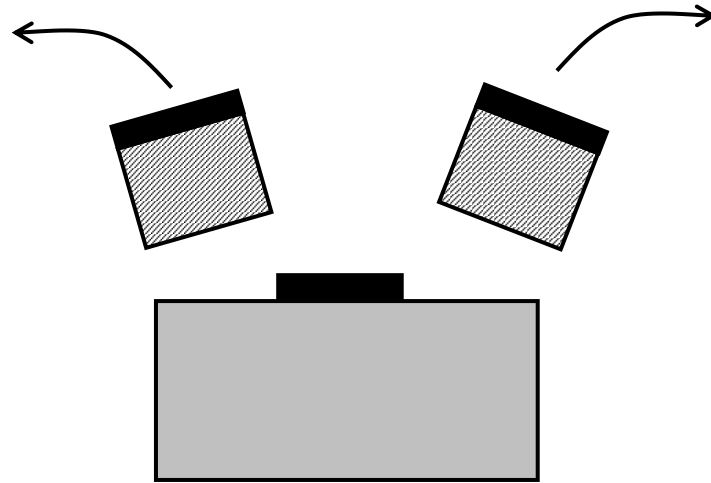


4. Resist image development
5. Metal etching (in acid)
6. Photoresist stripping

Alternative metal patterning: Lift-off



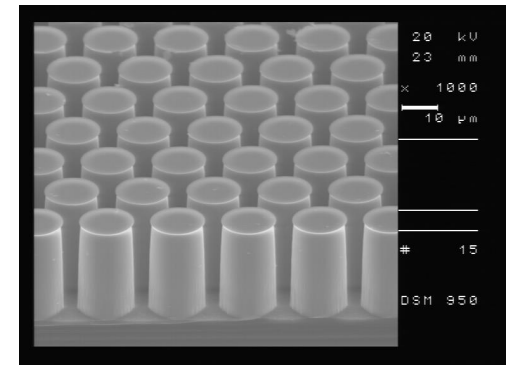
Litho + deposition



Resist lift-off

Silicon: pros and cons

- micromachining technologies exist
- surface modification technologies exist
- smooth and flat surfaces
- bonding to glass (400°C) and to silicon (1000°C)
- adhesive bonding to polymers
- integration of electrical, optical and thermal functions
- not transparent
- semiconducting
- 10-20 €/wafer (100 mm diameter)



PDMS: pros and cons

Easy processing by replica molding

Easily bondable, self adhesive

Optically transparent, electrical insulator

Biocompatible

Hydrophobic

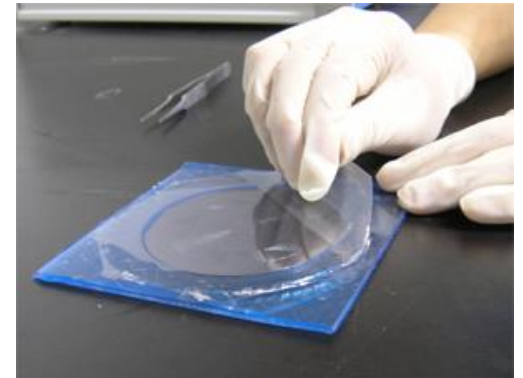
Oxygen and water vapor permeable

Absorbs solvents and salts

Max temperature $<100^{\circ}\text{C}$ (H_2O permeable...)

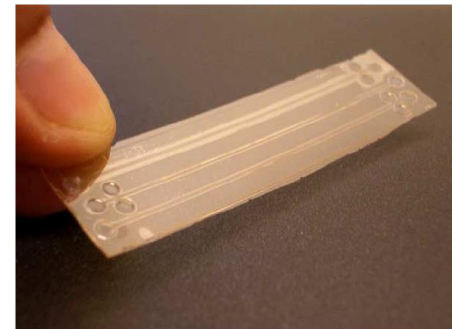
Huge thermal expansion $300 \text{ ppm}/^{\circ}\text{C}$

100-500 €/kg (1-5 €/100 mm diameter, 5 mm thick piece)



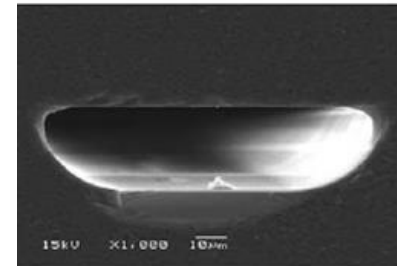
SU-8: pros & cons

- Easy to process; feature size and thickness range very large
- Thermally and chemically stable (for a polymer)
- Easy to bond to itself
- Not fully transparent & autofluorescence
- High stresses often encountered
➔ non-planarity



Glass: pros & cons

- Surface chemistry well known from lab glassware
- Transparent in VIS-IR
- If you need UV-transparency, use silica/quartz: pure SiO_2
- Difficult to etch, only isotropic shapes
- Anodic bonding to silicon easy & strong

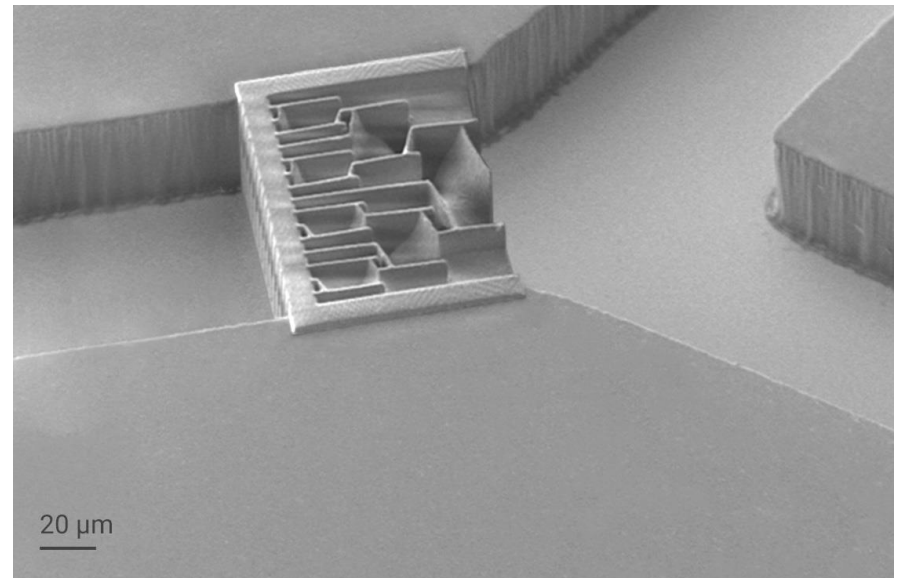


More exotic fabrication

Because feature sizes extremely small

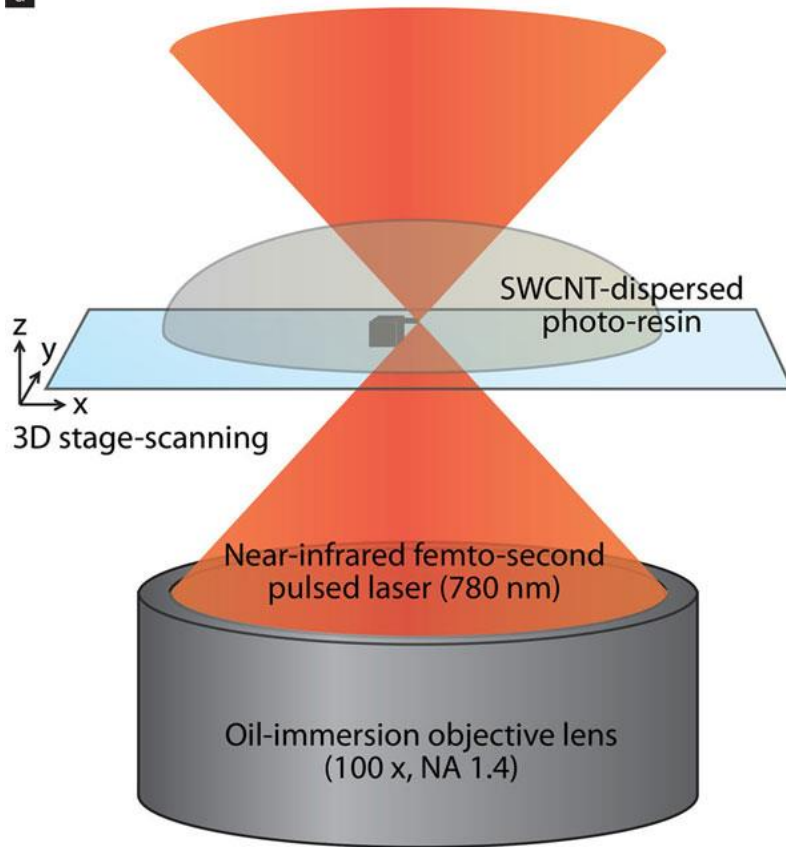
Because 3D structures

Maybe both !



2-photon photopolymerization (2PPP)

a

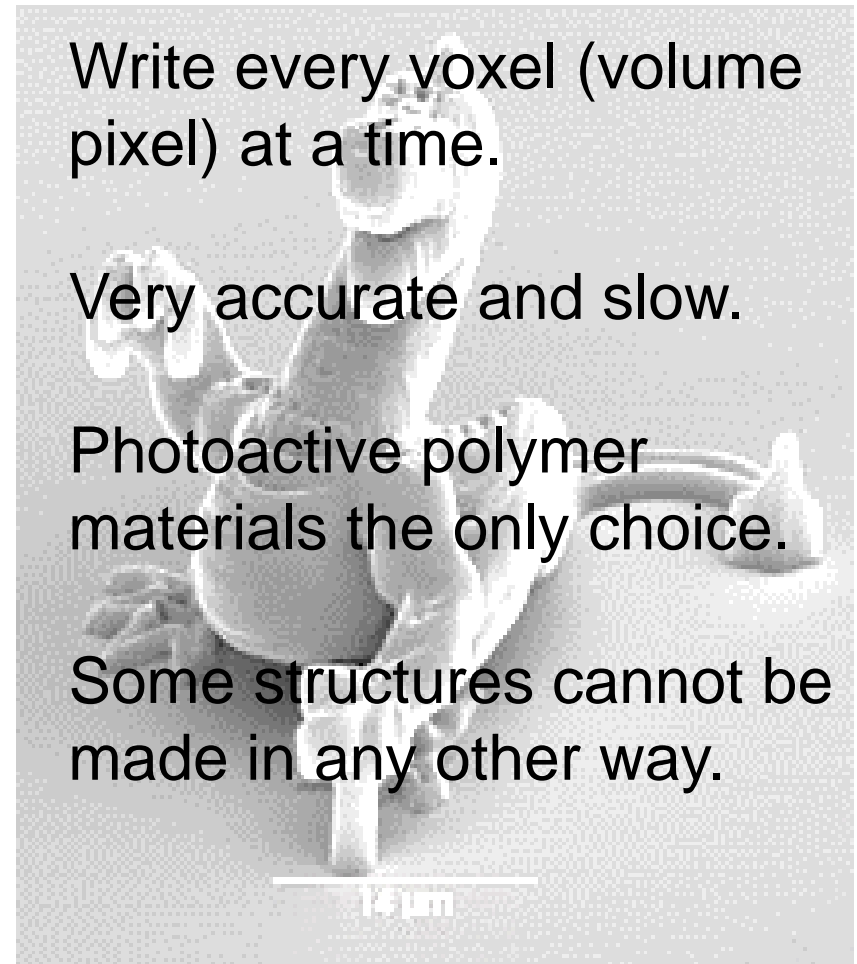


Write every voxel (volume pixel) at a time.

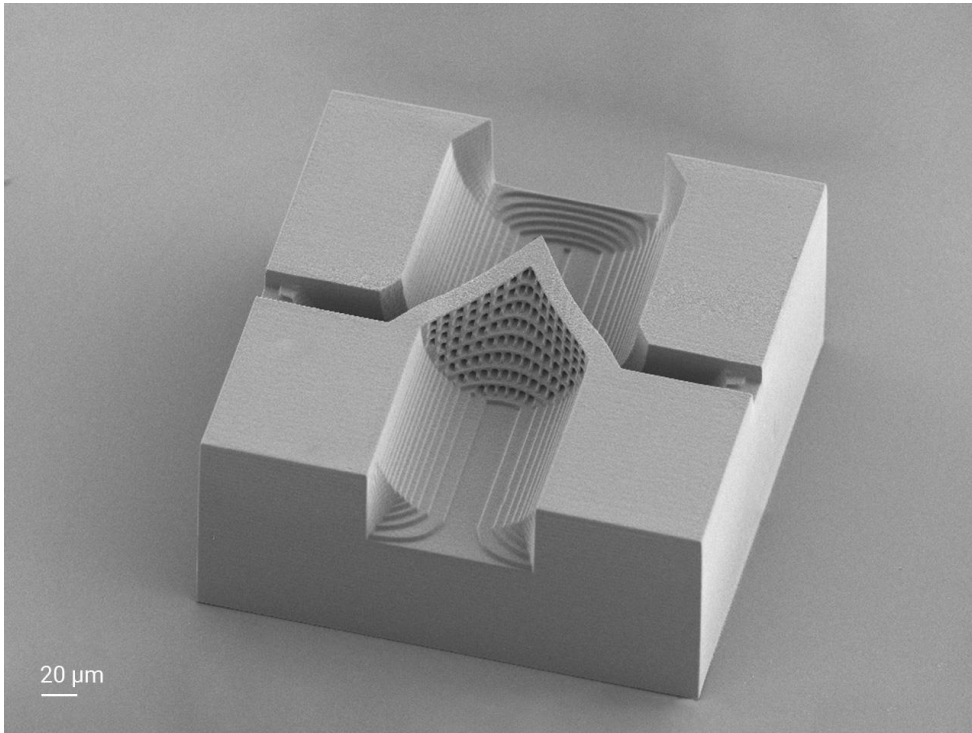
Very accurate and slow.

Photoactive polymer materials the only choice.

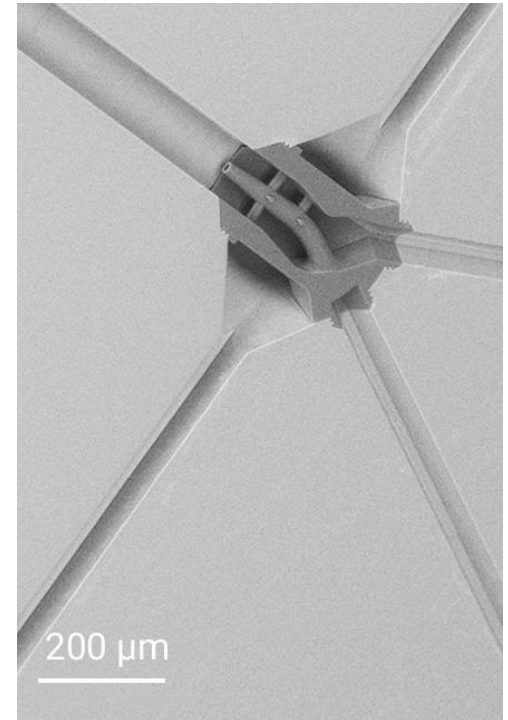
Some structures cannot be made in any other way.



Microfluidic filters by 2PPP



Sizes down to 100-200 nm.
Shape freedom.



Slow, and only
suitable for
experimentation.